To our customers,

Old Company Name in Catalogs and Other Documents

  On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

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April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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RENESAS

V853
32-BIT SINGLE-CHIP MICROCONTROLLERS

DESCRIPTION

The μPD70F3003A, μPD70F3025A, and μPD70F3003A(A) have a flash memory instead of the internal mask ROM of the μPD703003A/703004A, μPD703025A, and μPD703003A(A), respectively. This model is useful for small-scale production of a variety of application sets or early start of production since the program can be written and erased by the user even with the μPD70F3003 mounted on the board.

Detailed function descriptions are provided in the following user's manuals. Be sure to read them before designing.

V853 Hardware User's Manual:	**U10913E**
V850 Series Architecture User's Manual:	**U10243E**

FEATURES

• Compatible with μPD703003A, 703004A, 703025A, and 703003A(A)
  • Can be replaced with mask ROM model for mass production of application set
    μPD70F3003A → μPD703003A, 703004A
    μPD70F3025A → μPD703025A
    μPD70F3003A(A) → μPD703003A(A)
• Internal memory   Flash memory: 128KB (μPD70F3003A, 70F3003A(A))
                                                 256KB (μPD70F3025A)

Remark For differences among the products, refer to **1. DIFFERENCES BETWEEN PRODUCT**.

★   **ORDERING INFORMATION**

Part Number	Package	Quality Grade
μPD70F3003AGC-33-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Standard
μPD70F3003AGC-33-8EU-A	100-pin plastic LQFP (fine pitch) (14 × 14)	Standard
μPD70F3025AGC-33-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Standard
μPD70F3025AGC-33-8EU-A	100-pin plastic LQFP (fine pitch) (14 × 14)	Standard
μPD70F3003AGC(A)-33-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Special

Remarks 1. The μPD70F3003A and μPD70F3003A(A) differ in the quality grade only.
         2. Products with -A at the end of the part number are lead-free products.

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Electronics Corporation to know the specification of the quality grade on the devices and its recommended applications.

The mark ★ shows major revised points.

APPLICATIONS

μPD70F3003A, 70F3025A: Camcorders, VCRs, PPCs, LBPs, printers, motor controllers, NC machine
tools, mobile telephones, etc.

μPD70F3003A(A):   Medical equipment, automotive appliances, etc.

★ **PIN CONFIGURATION (Top View)**

- **100-Pin Plastic LQFP (fine pitch) (14 × 14)**
  μ**PD70F3003AGC-33-8EU** μ**PD70F3025AGC-33-8EU**
  μ**PD70F3003AGC-33-8EU-A** μ**PD70F3025AGC-33-8EU-A**
  μ**PD70F3003AGC(A)-33-8EU**

Top side pins (left to right, 100→76):
P30/TO130, P27/SCK1, P26/RXD1/SI1, P25/TXD1/SO1, P24/SCK0, P23/RXD0/SI0, P22/TXD0/SO0, P21/PWM1, P20/PWM0, NMI, V$_{DD}$, V$_{SS}$, P17/INTP123/SCK2, P16/INTP122/SI2, P15/INTP121/SO2, P14/INTP120, P13/TI12, P12/TCLR12, P11/TO121, P10/TO120, AV$_{DD}$, AV$_{SS}$, AV$_{REF1}$, P77/ANI7, P76/ANI6

Left side pins (1–25):
Pin	Signal
1	P31/TO131
2	P32/TCLR13
3	P33/TI13
4	P34/INTP130
5	P35/INTP131/SO3
6	P36/INTP132/SI3
7	P37/INTP133/SCK3
8	P63/A19
9	P62/A18
10	P61/A17
11	P60/A16
12	V$_{SS}$
13	V$_{DD}$
14	P57/AD15
15	P56/AD14
16	P55/AD13
17	P54/AD12
18	P53/AD11
19	P52/AD10
20	P51/AD9
21	P50/AD8
22	P47/AD7
23	P46/AD6
24	P45/AD5
25	P44/AD4

Right side pins (75–51):
Pin	Signal
75	P75/ANI5
74	P74/ANI4
73	P73/ANI3
72	P72/ANI2
71	P71/ANI1
70	P70/ANI0
69	ANO0
68	ANO1
67	AV$_{REF2}$
66	AV$_{REF3}$
65	P07/INTP113/ADTRG
64	P06/INTP112
63	P05/INTP111
62	P04/INTP110
61	P03/TI11
60	P02/TCLR11
59	P01/TO111
58	P00/TO110
57	P117/INTP143
56	P116/INTP142
55	P115/INTP141
54	P114/INTP140
53	P113/TI14
52	P112/TCLR14
51	P111/TO141

Bottom side pins (left to right, 26–50):
P43/AD3, P42/AD2, V$_{SS}$, V$_{DD}$, P41/AD1, P40/AD0, P90/LBEN, P91/UBEN, P92/R/W, P93/DSTB, P94/ASTB, P95/HLDAK, P96/HLDRQ, WAIT, V$_{PP}$, MODE, RESET, CV$_{DD}$/CKSEL, X2, X1, CV$_{SS}$, CLKOUT, V$_{SS}$, V$_{DD}$, P110/TO140

Caution   Connect V$_{PP}$ pin to V$_{SS}$ pin except the case that μ**PD70F3003A, 70F3003A(A) or 70F3025A**
is used in flash memory programming mode.

PIN NAMES

A16 to A19:	Address bus	P40 to P47:	Port 4
AD0 to AD15:	Address/data bus	P50 to P57:	Port 5
ADTRG:	A/D Trigger input	P60 to P63:	Port 6
ANI0 to ANI7:	Analog input	P70 to P77:	Port 7
ANO0, ANO1:	Analog output	P90 to P96:	Port 9
ASTB:	Address strobe	P110 to P117:	Port 11
AV_{DD}:	Analog V_{DD}	PWM0, PWM1:	Pulse width modulation
AV_{REF1} to AV_{REF3}:	Analog reference voltage	$\overline{RESET}$:	Reset
AV_{SS}:	Analog V_{SS}	R/$\overline{W}$:	Read/write status
CV_{DD}:	Power supply for clock generator	RXD0, PXD1:	Receive data
CV_{SS}:	Ground for clock generator	$\overline{SCK0}$ to $\overline{SCK3}$:	Serial clock
$\overline{CKSEL}$:	Clock select	SI0 to SI3:	Serial input
CLKOUT :	Clock output	SO0 to SO3:	Serial output
$\overline{DSTB}$:	Data strobe	TO110, TO111,	
$\overline{HLDAK}$:	Hold acknowledge	TO120, TO121,	
$\overline{HLDRQ}$:	Hold request	TO130, TO131,	
INTP110 to INTP113,		TO140, TO141:	Timer output
INTP120 to INTP123,		TCLR11 to TCLR14:	Timer clear
INTP130 to INTP133,		TI11 to TI14:	Timer input
INTP140 to INTP143:	Interrupt request from peripherals	TXD0, TXD1:	Transmit data
$\overline{LBEN}$:	Lower byte enable	$\overline{UBEN}$:	Upper byte enable
MODE:	Mode	$\overline{WAIT}$:	Wait
NMI:	Non-maskable interrupt request	X1, X2:	Crystal
P00 to P07:	Port 0	V_{DD}:	Power supply
P10 to P17:	Port 1	V_{PP}:	Programming power supply
P20 to P27:	Port 2	V_{SS}:	Ground
P30 to P37:	Port 3		

INTERNAL BLOCK DIAGRAM

Notes 1. μPD70F3003A, 70F3003A(A): 128 KB

        μPD70F3025A: 256 KB

   2. μPD70F3003A, 70F3003A(A): 4 KB

        μPD70F3025A: 8 KB
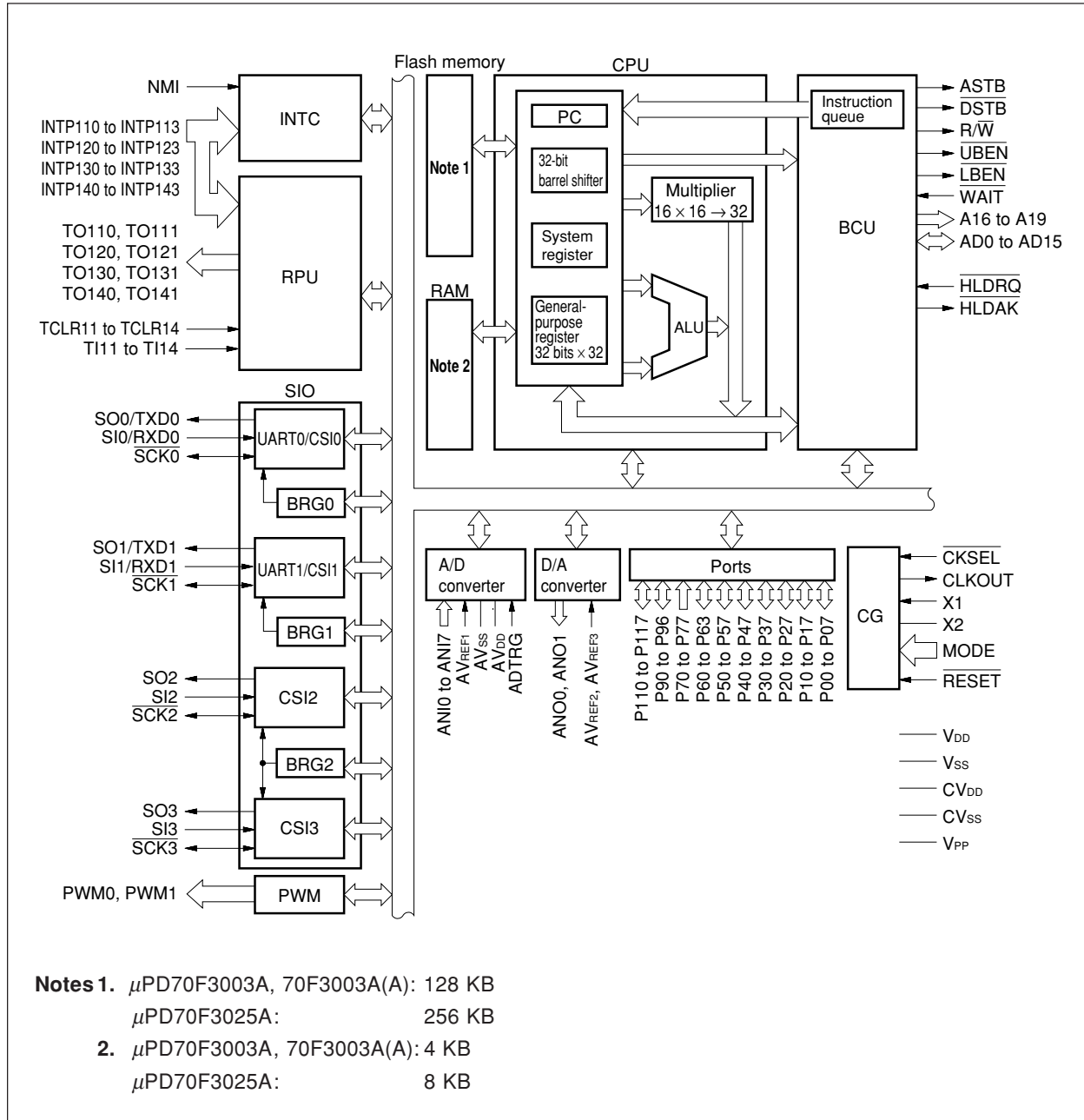
CONTENTS

1. DIFFERENCES BETWEEN PRODUCTS

Item	μPD703003A	μPD703004A	μPD703025A	μPD703003A(A)	μPD703025A(A)	μPD70F3003A	μPD70F3025A	μPD70F3003A(A)
Internal ROM	Mask ROM					Flash memory		
	128 KB	96 KB	256 KB	128 KB	256 KB	128 KB	256 KB	128 KB
Internal RAM	4 KB		8 KB	4 KB	8 KB	4 KB	8 KB	4 KB
Flash memory programming mode	None					Provided		
V_{PP} pin	None					Provided		
Quality grade	Standard			Special		Standard		Special
Electrical specifications	Current consumption, etc. differs. (Refer to each product data sheets).							
Others	Noise immunity and noise radiation differ because circuit scale and mask layout differ.							

Caution There are differences in noise immunity and noise radiation between the flash memory version and mask ROM version. When pre-producing an application set with the flash memory version and then mass-producing it with the mask ROM version, be sure to conduct sufficient evaluation for commercial samples (not engineering samples) of the mask ROM version.

2. PIN FUNCTIONS

2.1 Port Pins

(1/2)

Pin Name	I/O	Function	Alternate Function
P00	I/O	Port 0	TO110
P01		8-bit I/O port.	TO111
P02		Input/output can be specified in 1-bit units.	TCLR11
P03			TI11
P04			INTP110
P05			INTP111
P06			INTP112
P07			INTP113/ADTRG
P10	I/O	Port 1	TO120
P11		8-bit I/O port.	TO121
P12		Input/output can be specified in 1-bit units.	TCLR12
P13			TI12
P14			INTP120
P15			INTP121/SO2
P16			INTP122/SI2
P17			INTP123/$\overline{\text{SCK2}}$
P20	I/O	Port 2	PWM0
P21		8-bit I/O port.	PWM1
P22		Input/output can be specified in 1-bit units.	TXD0/SO0
P23			RXD0/SI0
P24			$\overline{\text{SCK0}}$
P25			TXD1/SO1
P26			RXD1/SI1
P27			$\overline{\text{SCK1}}$
P30	I/O	Port 3	TO130
P31		8-bit I/O port.	TO131
P32		Input/output can be specified in 1-bit units.	TCLR13
P33			TI13
P34			INTP130
P35			INTP131/SO3
P36			INTP132/SI3
P37			INTP133/$\overline{\text{SCK3}}$
P40 to P47	I/O	Port 4 8-bit I/O port. Input/output can be specified in 1-bit units.	AD0 to AD7
P50 to P57	I/O	Port 5 8-bit I/O port. Input/output can be specified in 1-bit units.	AD8 to AD15

(2/2)

Pin Name	I/O	Function	Alternate Function
P60 to P63	I/O	Port 6 4-bit I/O port. Input/output can be specified in 1-bit units.	A16 to A19
P70 to P77	Input	Port 7 8-bit input port.	ANI0 to ANI7
P90	I/O	Port 9 7-bit I/O port. Input/output can be specified in 1-bit units.	$\overline{\text{LBEN}}$
P91			$\overline{\text{UBEN}}$
P92			R/$\overline{\text{W}}$
P93			$\overline{\text{DSTB}}$
P94			ASTB
P95			$\overline{\text{HLDAK}}$
P96			$\overline{\text{HLDRQ}}$
P110	I/O	Port 11 8-bit I/O port. Input/output can be specified in 1-bit units.	TO140
P111			TO141
P112			TCLR14
P113			TI14
P114			INTP140
P115			INTP141
P116			INTP142
P117			INTP143

2.2 Non-Port Pins

<div align="right">(1/2)</div>

Pin Name	I/O	Function	Alternate Function
TO110	Output	Pulse signal output from timers 11 to 14	P00
TO111			P01
TO120			P10
TO121			P11
TO130			P30
TO131			P31
TO140			P110
TO141			P111
TCLR11	Input	External clear signal input for timers 11 to 14	P02
TCLR12			P12
TCLR13			P32
TCLR14			P112
TI11	Input	External count clock input for timers 11 to 14	P03
TI12			P13
TI13			P33
TI14			P113
INTP110	Input	External maskable interrupt request input and external capture trigger input for timer 11	P04
INTP111			P05
INTP112			P06
INTP113			P07/ADTRG
INTP120	Input	External maskable interrupt request input and external capture trigger input for timer 12	P14
INTP121			P15/SO2
INTP122			P16/S12
INTP123			P17/$\overline{\text{SCK2}}$
INTP130	Input	External maskable interrupt request input and external capture trigger input for timer 13	P34
INTP131			P35/SO3
INTP132			P36/SI3
INTP133			P37/$\overline{\text{SCK3}}$
INTP140	Input	External maskable interrupt request input and external capture trigger input for timer 14	P114
INTP141			P115
INTP142			P116
INTP143			P117
SO0	Output	Serial transmit data output for CSI0 to CSI3 (3-wire)	P22/TXD0
SO1			P25/TXD1
SO2			P15/INTP121
SO3			P35/INTP131
SI0	Input	Serial receive data output for CSI0 to CSI3 (3-wire)	P23/RXD0
SI1			P26/RXD1
SI2			P16/INTP122
SI3			P36/INTP132

Pin Name	I/O	Function	Alternate Function
$\overline{SCK0}$	I/O	Serial clock I/O for CSI0 to CSI3 (3-wire)	P24
$\overline{SCK1}$			P27
$\overline{SCK2}$			P17/INTP123
$\overline{SCK3}$			P37/INTP133
TXD0	Output	Serial transmit data output of UART0 to UART1	P22/SO0
TXD1			P25/SO1
RXD0	Input	Serial receive data input of UART0 to UART1	P23/SI0
RXD1			P26/SI1
PWM0	Output	Pulse signal output of PWM	P20
PWM1			P21
AD0 to AD7	I/O	16-bit multiplexed address/data bus when external memory is connected	P40 to P47
AD8 to AD15			P50 to P57
A16 to A19	Output	Higher address bus when external memory is connected	P60 to P63
$\overline{LBEN}$	Output	Lower byte enable signal output of external data bus	P90
$\overline{UBEN}$		Higher byte enable signal output of external data bus	P91
$R/\overline{W}$	Output	External read/write status output	P92
$\overline{DSTB}$		External data strobe signal output	P93
ASTB		External address strobe signal output	P94
$\overline{HLDAK}$	Output	Bus hold acknowledge output	P95
$\overline{HLDRQ}$	Input	Bus hold request input	P96
ANI0 to ANI7	Input	Analog input to A/D converter	P70 to P77
ANO0, ANO1	Output	Analog output of D/A converter	—
NMI	Input	Non-maskable interrupt request input	—
CLKOUT	Output	System clock output	—
$\overline{CKSEL}$	Input	Input specifying operation mode of clock generator	CV_{DD}
$\overline{WAIT}$	Input	Control signal input inserting wait state in bus cycle	—
MODE	Input	Operation mode specification	—
$\overline{RESET}$	Input	System reset input	—
X1	Input	System clock resonator connection. Input external clock to X1 to	—
X2	—	supply external clock.	—
ADTRG	Input	A/D converter external trigger input	P07/INTP113
AV_{REF1}	Input	Reference voltage input for A/D converter	—
AV_{REF2}	Input	Reference voltage input for D/A converter	—
AV_{REF3}			—
AV_{DD}	—	Positive power supply for A/D converter	—
AV_{SS}	—	Ground potential for A/D converter	—
CV_{DD}	—	Positive power supply for internal clock generator	$\overline{CKSEL}$
CV_{SS}	—	Ground potential for internal clock generator	—
V_{DD}	—	Positive power supply	—
V_{SS}	—	Ground potential	—
V_{PP}	—	High voltage application pin when program is written/verified	—

2.3 Pin I/O Circuits and Recommended Connection of Unused Pins

Table 2-1 shows the I/O circuit type of each pin, and the recommended connections of the unused pins. Figure 2-1 shows a partially simplified diagram of each circuit.

It is recommended that 1 to 10 kΩ resistors be used when connecting to V_{DD} or V_{SS} via a resistor.

Table 2-1. Types of Pin I/O Circuits and Recommended Connections of Unused Pins (1/2)

Pin Name	I/O Circuit Type	Recommended Connection of Unused Pins
P00/TO110, P01/TO111	5	Input:　　Independently connect to V_{DD} or V_{SS} via a resistor.
P02/TCLR11, P03/TI11, P04/INTP110 to P07/INTP113/ADTRG	8	Output:　Leave open.
P10 to TO120, P11/TO121	5	
P12/TCLR12, P13/TI12 P14/INTP120 P15/INTP121/SO2 P16/INTP122/SI2 P17/INTP123/$\overline{SCK2}$	8	
P20/PWM0, P21/PWM1 P22/TXD0/SO0	5	
P23/RXD0/SI0, P24/$\overline{SCK0}$	8	
P25/TXD1/SO1	5	
P26/RXD1/SI1, P27/$\overline{SCK1}$	8	
P30/TO130, P31/TO131	5	
P32/TCLR13, P33/TI13 P34/INTP130	8	
P35/INTP131/SO3 P36/INTP132/SI3 P37/INTP133/$\overline{SCK3}$	10-A	
P40/AD0 to P47/AD7	5	
P50/AD8 to P57/AD15		
P60/A16 to P63/A19		
P70/ANI0 to P77/ANI7	9	Directly connect to V_{SS}.
P90/$\overline{LBEN}$	5	Input:　　Independently connect to V_{DD} or V_{SS} via a resistor.
P91/$\overline{UBEN}$		Output:　Leave open.
P92/R/$\overline{W}$		
P93/$\overline{DSTB}$		
P94/ASTB		
P95/$\overline{HLDAK}$		
P96/$\overline{HLDRQ}$		
P110/TO140, P111/TO141		
P112/TCLR14, P113/TI14 P114/INTP140 to P117/INTP143	8	

Table 2-1. Types of Pin I/O Circuits and Recommended Connection of Unused Pins (2/2)

Pin Name	I/O Circuit Type	Recommended Connection of Unused Pins
ANO0, ANO1	12	Leave open.
NMI	2	Directly connect to V_{SS}.
CLKOUT	3	Leave open.
$\overline{\text{WAIT}}$	1	Directly connect to V_{DD}.
MODE	2	—
$\overline{\text{RESET}}$		
$CV_{DD}/\overline{\text{CKSEL}}$		—
AV_{REF1} to AV_{REF3}, AV_{SS}	—	Directly connect to V_{SS}.
AV_{DD}	—	Directly connect to V_{DD}.
V_{PP}	—	Connect to V_{SS}.

Figure 2-1. Pins I/O Circuits

Type 1

Type 8

Type 2

Schmitt trigger input with hysteresis characteristics

Type 9

Type 3

Type 10-A

Type 5

Type 12
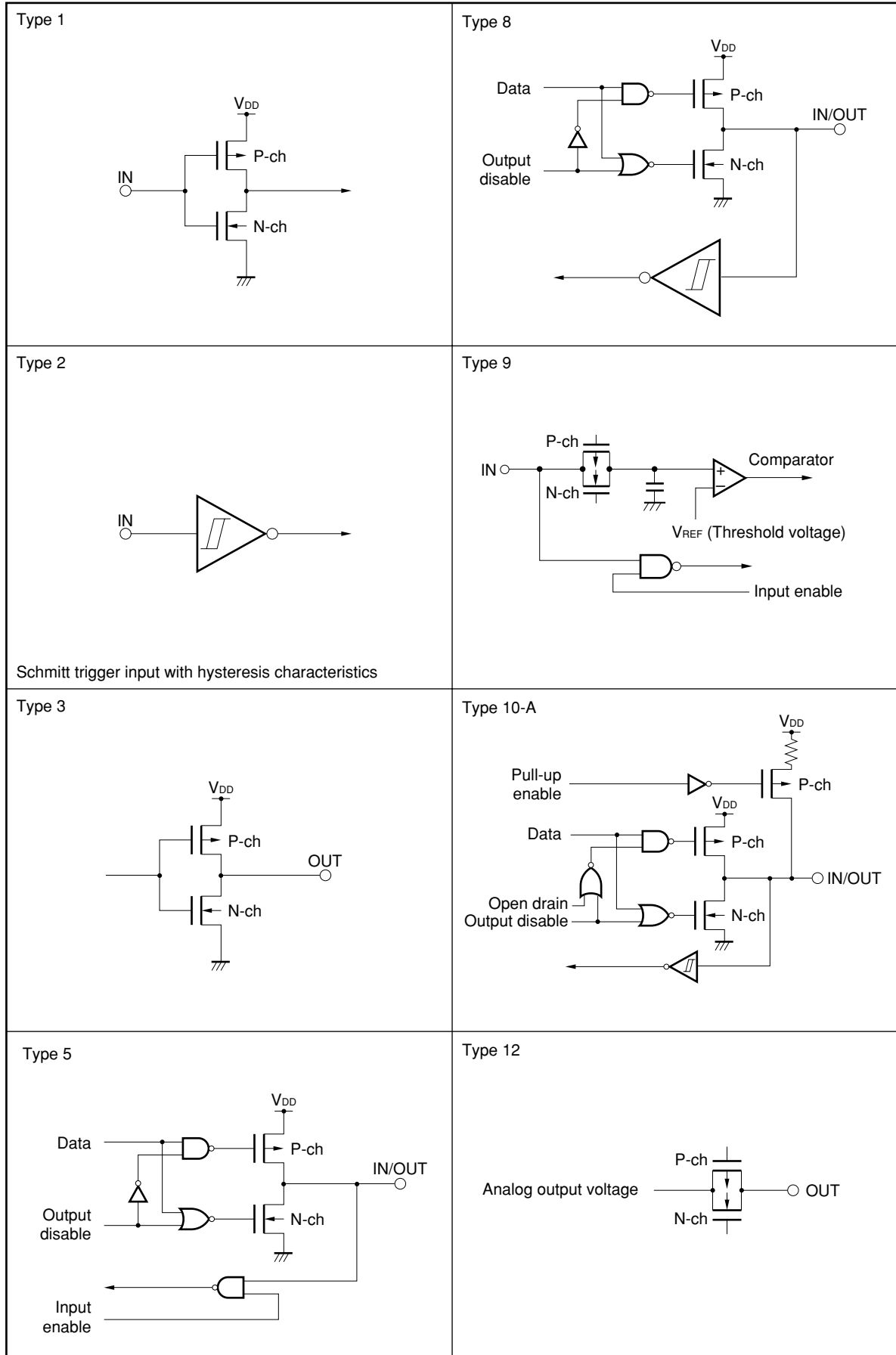
3. ELECTRICAL SPECIFICATIONS

3.1 Normal Operation Mode

Absolute Maximum Ratings (T$_A$ = 25°C)

Parameter	Symbol	Conditions		Ratings	Unit
Supply voltage	V$_{DD}$	V$_{DD}$ pin		-0.5 to $+7.0$	V
	CV$_{DD}$	CV$_{DD}$ pin		-0.5 to V$_{DD}$ + 0.3[Note 1]	V
	CV$_{SS}$	CV$_{SS}$ pin		-0.5 to $+0.5$	V
	AV$_{DD}$	AV$_{DD}$ pin		-0.5 to V$_{DD}$ + 0.3[Note 1]	V
	AV$_{SS}$	AV$_{SS}$ pin		-0.5 to $+0.5$	V
Input voltage	V$_{I1}$	**Note 2**, V$_{DD}$ = 5.0 V $\pm$10%		-0.5 to V$_{DD}$ + 0.3[Note 1]	V
	V$_{I2}$	V$_{PP}$ pin in flash memory programming mode, V$_{DD}$ = 5.0 V $\pm$10%		-0.5 to $+11.0$	V
Clock input voltage	V$_K$	X1 pin, V$_{DD}$ = 5.0 V $\pm$10%		-0.5 to V$_{DD}$ + 1.0[Note 1]	V
Output current, low	I$_{CL}$	1 pin		4.0	mA
		Total of all pins		100	mA
Output current, high	I$_{CH}$	1 pin		-4.0	mA
		Total of all pins		-100	mA
Output voltage	V$_O$	V$_{DD}$ = 5.0 V $\pm$10%		-0.5 to V$_{DD}$ + 0.3[Note 1]	V
Analog input voltage	V$_{IAN}$	P70/ANI0 to P77/ANI7	AV$_{DD}$ > V$_{DD}$	-0.5 to V$_{DD}$ + 0.3[Note 1]	V
			V$_{DD}$ $\geq$ AV$_{DD}$	-0.5 to AV$_{DD}$ + 0.3[Note 1]	V
Analog reference input voltage	AV$_{REF}$	AV$_{REF1}$ to AV$_{REF3}$	AV$_{DD}$ > V$_{DD}$	-0.5 to V$_{DD}$ + 0.3[Note 1]	V
			V$_{DD}$ $\geq$ AV$_{DD}$	-0.5 to AV$_{DD}$ + 0.3[Note 1]	V
Operating ambient temperature	T$_A$			-40 to $+85$	$^\circ$C
Storage temperature	T$_{stg}$			-65 to $+125$	$^\circ$C

Notes 1. Be sure not to exceed the absolute maximum ratings (MAX. value) of each supply voltage.

2. X1, P70 to P77, AV$_{REF1}$ to AV$_{REF3}$, and their alternate-function pins are excluded.

Cautions 1. Avoid direct connections among the IC device output (or I/O) pins and between V$_{DD}$ or V$_{CC}$ and GND. However, direct connections among open-drain and open-collector pins are possible, as are direct connections to external circuits that have timing designed to prevent output conflict with pins that become high-impedance.

2. Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
The normal operating ranges of ratings and conditions in which the quality of the product is guaranteed are specified in the following DC Characteristics and AC Characteristics.

Capacitance (T_A = 25°C, V_DD = V_SS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C_I	fc = 1 MHz			15	pF
I/O capacitance	C_{IO}	Pins other than tested pin: 0 V			15	pF
Output capacitance	C_O				15	pF

Operating Conditions

Operation Mode	Internal System Clock Frequency (ϕ)	Operating Temperature (T_A)	Supply Voltage (V_{DD})
Direct mode, PLL mode	2 to 33 MHz[Note 1]	−40 to +85°C	5.0 V ±10%
	5 to 33 MHz[Note 2]	−40 to +85°C	5.0 V ±10%

Notes 1. When A/D converter not used.
2. When A/D converter used.

Recommended Oscillator

Caution For the resonator selection and oscillator constant of the μPD70F3003A(A), customers are requested to apply to the resonator manufacturer for evaluation.

(1) Ceramic resonator connection (T_A = −40 to +85°C)

(a) μPD70F3003A

Manufacturer	Part Number	Oscillation Frequency fxx (MHz)	Recommended Circuit Constant			Oscillation Voltage Range		Oscillation Stabilization Time (MAX.) T_OST (ms)
			C1 (pF)	C2 (pF)	R_d (W)	MIN. (V)	MAX. (V)	
Kyocera Corporation	PBRC4.00HR	4.0	On-chip	On-chip	—	4.5	5.5	0.10
	PBRC5.00HR	5.0	On-chip	On-chip	—	4.5	5.5	0.08
	PBRC6.00HR	6.0	On-chip	On-chip	—	4.5	5.5	0.08
	PBRC6.60HR	6.6	On-chip	On-chip	—	4.5	5.5	0.08
TDK	FCR4.0MC5	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	FCR5.0MC5	5.0	On-chip	On-chip	—	4.5	5.5	0.14
	FCR6.0MC5	6.0	On-chip	On-chip	—	4.5	5.5	0.11
Murata Mfg. Co., Ltd	CSTS0400MG06	4.0	On-chip	On-chip	—	4.5	5.5	0.12
	CSTCR4M00G05	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	CSTS0600MG06	6.0	On-chip	On-chip	—	4.5	5.5	0.14
	CSTCR6M00G55-R0	6.0	On-chip	On-chip	—	4.5	5.5	0.18

Cautions 1. Connect the oscillator as closely to the X1 and X2 pins as possible.
2. Do not wire any other signal lines in the area indicated by the broken lines.
3. Thoroughly evaluate the matching between the μPD70F3003A and the resonator.

(b) μ**PD70F3025A**

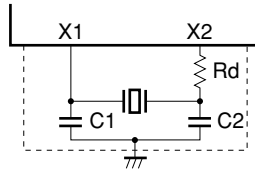| Manufacturer	Part Number	Oscillation Frequency fxx (MHz)	Recommended Circuit Constant			Oscillation Voltage Range		Oscillation Stabilization Time (MAX.) TOST (ms)
			C1 (pF)	C2 (pF)	Rd (W)	MIN. (V)	MAX. (V)	
Kyocera	PBRC4.00HR	4.0	On-chip	On-chip	—	4.5	5.5	0.12
Corporation	PBRC5.00HR	5.0	On-chip	On-chip	—	4.5	5.5	0.04
	PBRC6.00HR	6.0	On-chip	On-chip	—	4.5	5.5	0.04
	PBRC6.60HR	6.6	On-chip	On-chip	—	4.5	5.5	0.04
TDK	FCR4.0MC5	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	FCR5.0MC5	5.0	On-chip	On-chip	—	4.5	5.5	0.13
	FCR6.0MC5	6.0	On-chip	On-chip	—	4.5	5.5	0.13
Murata Mfg.	CSTS0400MG06	4.0	On-chip	On-chip	—	4.5	5.5	0.12
Co., Ltd	CSTCR4M00G55-R0	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	CSTS0600MG06	6.0	On-chip	On-chip	—	4.5	5.5	0.16
	CSTCR6M00G55-R0	6.0	On-chip	On-chip	—	4.5	5.5	0.19

Cautions 1. Connect the oscillator as closely to the X1 and X2 pins as possible.

2. Do not wire any other signal lines in the area indicated by the broken lines.

3. Thoroughly evaluate the matching between the μPD70F3025A and the resonator.

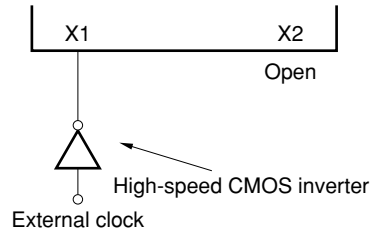**(2) External clock input**

Cautions 1. Put the high-speed CMOS inverter as close to the X1 pins as possible.

2. Sufficiently evaluate the matching between the μPD70F3003A, 70F3025A, or 70F3003A(A), and the high-speed CMOS inverter.

DC Characteristics (T$_A$ = –40 to +85°C, V$_{DD}$ = 5.0 V ±10%, V$_{SS}$ = 0 V)

(1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V$_{IH}$	Except X1 and **Note**	2.2		V$_{DD}$ + 0.3	V
		Note	0.8V$_{DD}$		V$_{DD}$ + 0.3	V
Input voltage, low	V$_{IL}$	Except X1 and **Note**	–0.5		+0.8	V
		Note	–0.5		0.2V$_{DD}$	V
Clock input voltage, high	V$_{XH}$	X1	0.8V$_{DD}$		V$_{DD}$ + 0.5	V
Clock input voltage, low	V$_{XL}$	X1	–0.5		0.6	V
Schmitt trigger input threshold voltage	V$_T{}^+$	**Note**, rising		3.0		V
	V$_T{}^-$	**Note**, falling		2.0		V
Schmitt trigger input hysteresis width	V$_T{}^+$ – V$_T{}^-$	**Note**	0.5			V
Output voltage, high	V$_{OH}$	I$_{OH}$ = –2.5 mA	0.7V$_{DD}$			V
		I$_{OH}$ = –100 μA	V$_{DD}$ – 0.4			V
Output voltage, low	V$_{OL}$	I$_{OC}$ = 2.5 mA			0.45	V
Input leakage current, high	I$_{LIH}$	V$_I$ = V$_{DD}$			10	μA
Input leakage current, low	I$_{LIL}$	V$_I$ = 0 V			–10	μA
Output leakage current, high	I$_{LOH}$	V$_O$ = V$_{DD}$			10	μA
Output leakage current, low	I$_{LOL}$	V$_O$ = 0 V			–10	μA
Software pull-up resistor	R	P35/INTP131/SO3, P36/INTP132/SI3, P37/INTP133/$\overline{\text{SCK3}}$	15	40	90	kΩ

Note   P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{\text{RESET}}$, NMI, MODE, and their alternate-function pins.

Remark   TYP. values are reference values for when T$_A$ = 25°C and V$_{DD}$ = 5.0 V.

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply current	μPD70F3003A, 70F3003A(A)	Operating	I_{DD1}	Direct mode		$2.2 \times \phi + 7.5$	$2.5 \times \phi + 22$	mA
				PLL mode		$2.3 \times \phi + 9.5$	$2.6 \times \phi + 25$	mA
		In HALT mode	I_{DD2}	Direct mode		$1.2 \times \phi + 7.5$	$1.3 \times \phi + 15$	mA
				PLL mode		$1.3 \times \phi + 9.5$	$1.4 \times \phi + 17$	mA
		In IDLE mode	I_{DD3}	Direct mode		$8 \times \phi + 300$	$10 \times \phi + 500$	μA
				PLL mode		$0.1 \times \phi + 2$	$0.2 \times \phi + 3$	mA
		In STOP mode	I_{DD4}	CESEL = 0, **Note 1**		2	50	μA
				CESEL = 0, **Note 2**		2	200	μA
				CESEL = 1, **Note 1**		30	200	μA
				CESEL = 1, **Note 2**		30	500	μA
	μPD70F3025A	Operating	I_{DD1}	Direct mode		$2.5 \times \phi + 8$	$2.8 \times \phi + 22.5$	mA
				PLL mode		$2.6 \times \phi + 10$	$2.9 \times \phi + 25.5$	mA
		In HALT mode	I_{DD2}	Direct mode		$1.3 \times \phi + 7.5$	$1.4 \times \phi + 15$	mA
				PLL mode		$1.3 \times \phi + 12.5$	$1.4 \times \phi + 20$	mA
		In IDLE mode	I_{DD3}	Direct mode		$8 \times \phi + 300$	$10 \times \phi + 500$	μA
				PLL mode		$0.1 \times \phi + 2$	$0.2 \times \phi + 3$	mA
		In STOP mode	I_{DD4}	CESEL = 0, **Note 1**		2	50	μA
				CESEL = 0, **Note 2**		2	200	μA
				CESEL = 1, **Note 1**		60	300	μA
				CESEL = 1, **Note 2**		60	500	μA

Notes 1. $-40°C \leq T_A \leq +50°C$

2. $50°C < T_A \leq 85°C$

Remarks 1. TYP. values are reference values for when $T_A = 25°C$ (except for the conditions in **Note 2**) and V_{DD} = 5.0 V. The power supply current does not include AV_{REF1} to AV_{REF3} or the current that flows through software pull-up resistors.

2. ϕ: Internal system clock frequency

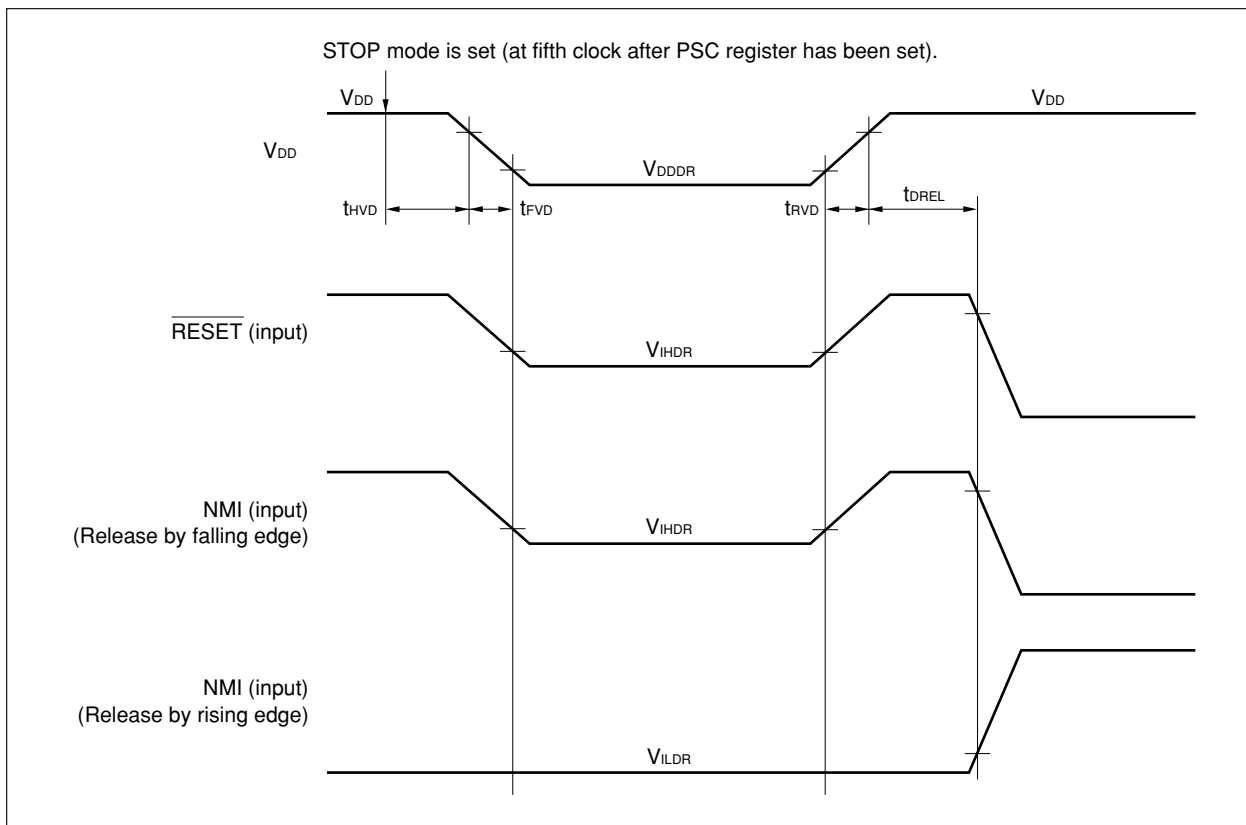**Data Retention Characteristics (T$_A$ = –40 to +85°C, V$_{DD}$ = V$_{DDDR}$)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Data hold voltage	V$_{DDDR}$	STOP mode		1.5		5.5	V
Data hold current	I$_{DDDR}$	μPD70F3003A, 70F3003A(A)	CESEL = 0, **Note 1**		0.4V$_{DDDR}$	50	μA
			CESEL = 0, **Note 2**		0.4V$_{DDDR}$	200	μA
			CESEL = 1, **Note 1**		6V$_{DDDR}$	200	μA
			CESEL = 1, **Note 2**		6V$_{DDDR}$	500	μA
		μPD70F3025A	CESEL = 0, **Note 1**		0.4V$_{DDDR}$	50	μA
			CESEL = 0, **Note 2**		0.4V$_{DDDR}$	200	μA
			CESEL = 1, **Note 1**		12V$_{DDDR}$	300	μA
			CESEL = 1, **Note 2**		12V$_{DDDR}$	500	μA
Supply voltage rise time	t$_{RVD}$			200			μs
Supply voltage fall time	t$_{FVD}$			200			μs
Supply voltage hold time (vs. STOP mode setting)	t$_{HVD}$			0			ms
STOP mode release signal input time	t$_{DREL}$			0			ns
Data hold input voltage, high	V$_{IHDR}$	**Note 3**		0.9V$_{DDDR}$		V$_{DDDR}$	V
Data hold input voltage, low	V$_{ILDR}$	**Note 3**		0		0.1V$_{DDDR}$	V

Notes 1. –40°C ≤ T$_A$ ≤ +50°C

2. 50°C <T$_A$ ≤ 85°C

3. P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{RESET}$, NMI, MODE, X1, and their alternate-function pins.

Remark TYP. values are reference values for when T$_A$ = 25°C (except for the conditions in **Note 2**) and V$_{DD}$ = 5.0 V.

STOP mode is set (at fifth clock after PSC register has been set).

AC Characteristics (T$_A$ = –40 to +85°C, V$_{DD}$ = 5.0 V ±10%, V$_{SS}$ = 0 V)

AC test input test points

(a) **P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{RESET}$, NMI, MODE, X1, and their alternate-function pins**

V$_{DD}$ 0.8V$_{DD}$ 0.8V$_{DD}$

             0.2V$_{DD}$ Test points   0.2V$_{DD}$

0 V

(b) **Other than (a)**

2.4 V   2.2 V   2.2 V

        0.8 V   Test points   0.8 V

0.4 V
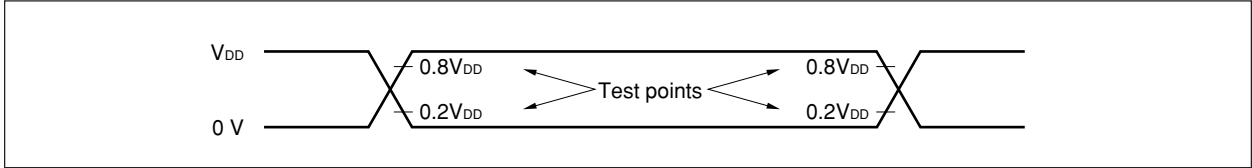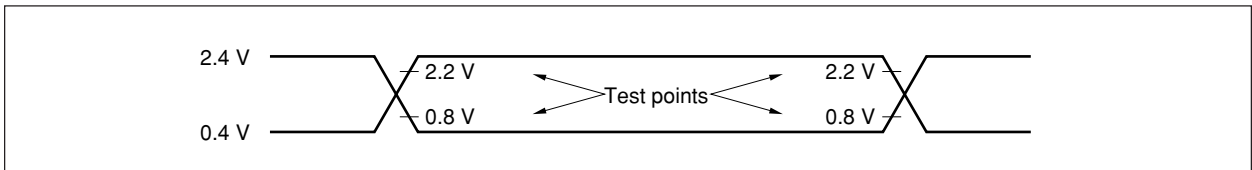
AC test output test points

2.2 V   2.2 V

0.8 V   Test points   0.8 V

Load condition

DUT
(tested device)

C$_L$ = 50 pF

Caution If the load capacitance exceeds 50 pF due to the circuit configuration, decrease the load capacitance of this device to less then 50 pF by using a buffer.

(1) Clock timing

Parameter		Symbol	Conditions	MIN.	MAX.	Unit
X1 input cycle	<1>	t_{CYX}	Direct mode	15	**Note 1**	ns
			PLL mode (PLL lock status)	151[Note 2]	**Note 3**	ns
X1 input width, high	<2>	t_{WXH}	Direct mode	6		ns
			PLL mode	60		ns
X1 input width, low	<3>	t_{WXL}	Direct mode	6		ns
			PLL mode	60		ns
X1 input rise time	<4>	t_{XR}	Direct mode		7	ns
			PLL mode		10	ns
X1 input fall time	<5>	t_{XF}	Direct mode		7	ns
			PLL mode		10	ns
CPU operating frequency	—	ϕ		**Note 4**	33	MHz
CLKOUT output cycle	<6>	t_{CYK}		30	**Note 5**	ns
CLKOUT width, high	<7>	t_{WKH}		0.5 T − 5		ns
CLKOUT width, low	<8>	t_{WKL}		0.5 T − 5		ns
CLKOUT rise time	<9>	t_{XR}			5	ns
CLKOUT fall time	<10>	t_{XF}			5	ns
X1 ↓→ CLKOUT delay time	<11>	t_{DXK}	Direct mode	3	17	ns

Notes 1. When A/D converter used: 100 ns

When A/D converter not used: 250 ns

2. When using A/D converter: The value when $\phi = 5 \times f_{XX}$ and $\phi = f_{XX}$ are set. Setting $\phi = 1/2 \times f_{XX}$ is prohibited.

When not using A/D converter: The value when $\phi = 5 \times f_{XX}$, $\phi = f_{XX}$, and $\phi = 1/2 \times f_{XX}$ are set.

3. When using A/D converter: 250 ns (when $\phi = 5 \times f_{XX}$ is set) and 200 ns (when $\phi = f_{XX}$ is set). Setting $\phi = 1/2 \times f_{XX}$ is prohibited.

When not using A/D converter: 250 ns (when $\phi = 5 \times f_{XX}$, $\phi = f_{XX}$, and $\phi = 1/2 \times f_{XX}$ are set).

4. When A/D converter used: 5 MHz

When A/D converter not used: 2 MHz

5. When A/D converter used: 200 ns

When A/D converter not used: 500 ns

Remark T = t_{CYK}
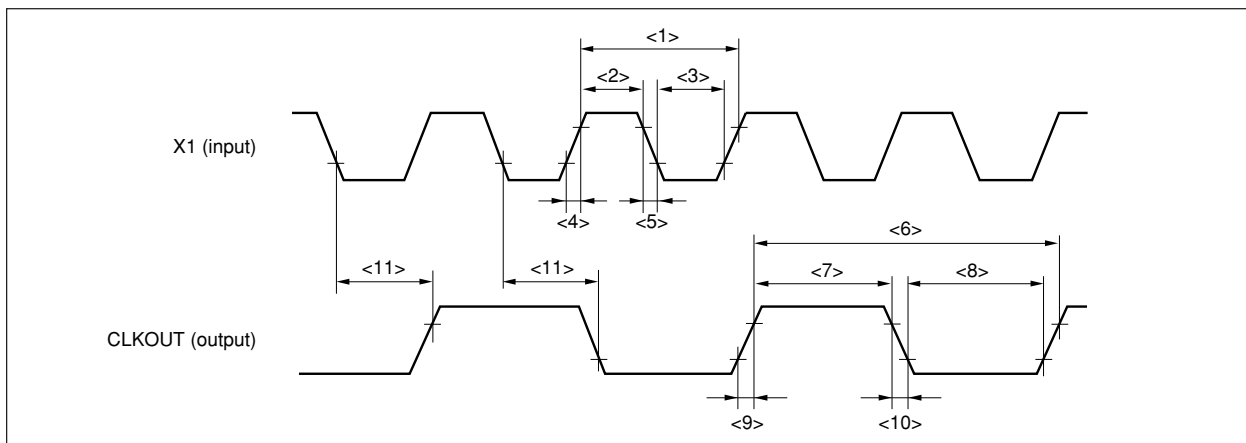
(2) Input wave

(a) P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{\text{RESET}}$, NMI, MODE, and their alternate-function pins
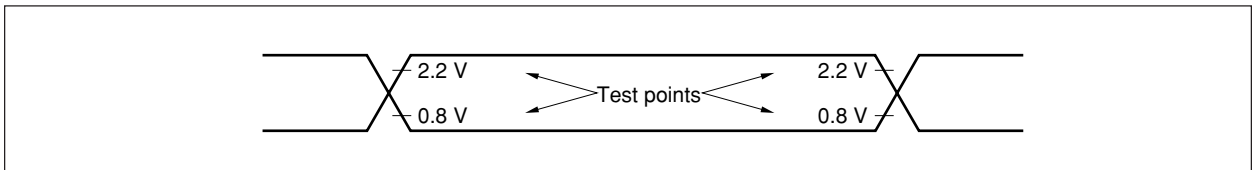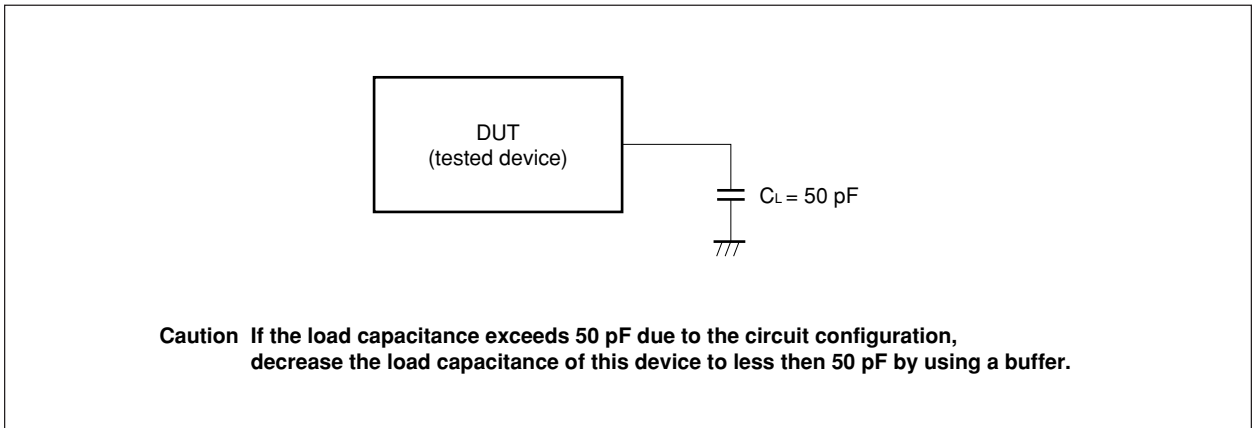
Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Input rise time	<12>	t_{IR2}			20	ns
Input fall time	<13>	t_{IF2}			20	ns
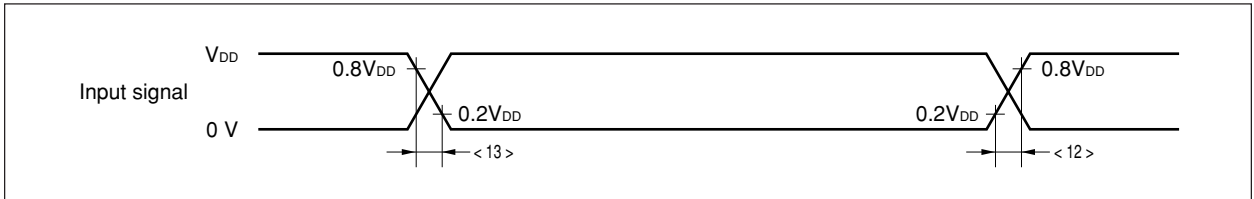
(b) Other than (a)

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Input rise time	<14>	t_{IR1}			10	ns
Input fall time	<15>	t_{IF1}			10	ns
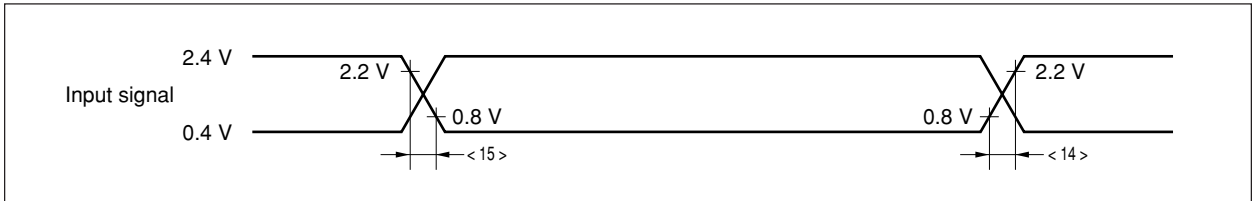
(3) Output wave (other than CLKOUT)

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Output rise time	<16>	t_{OR}			10	ns
Output fall time	<17>	t_{OF}			10	ns
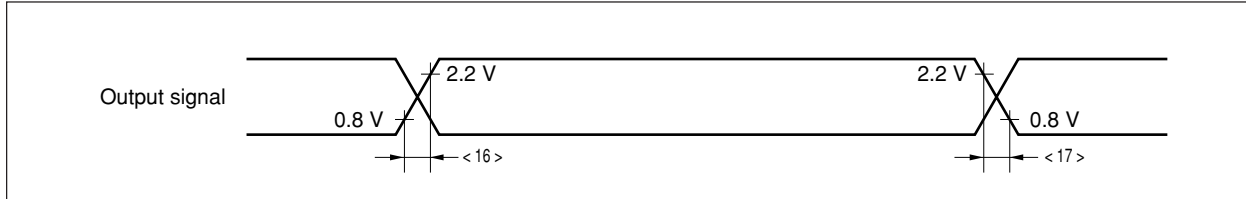
(4) Reset timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{\text{RESET}}$ width, high	<18>	t_{WRSH}		500		ns
$\overline{\text{RESET}}$ width, low	<19>	t_{WRSL}	On power application, or on releasing STOP mode	$500 + T_{OST}$		ns
			Except on power application, or except on releasing STOP mode	500		ns

Remark T_{OST}: Oscillation stabilization time

(5) Read timing (1/2)

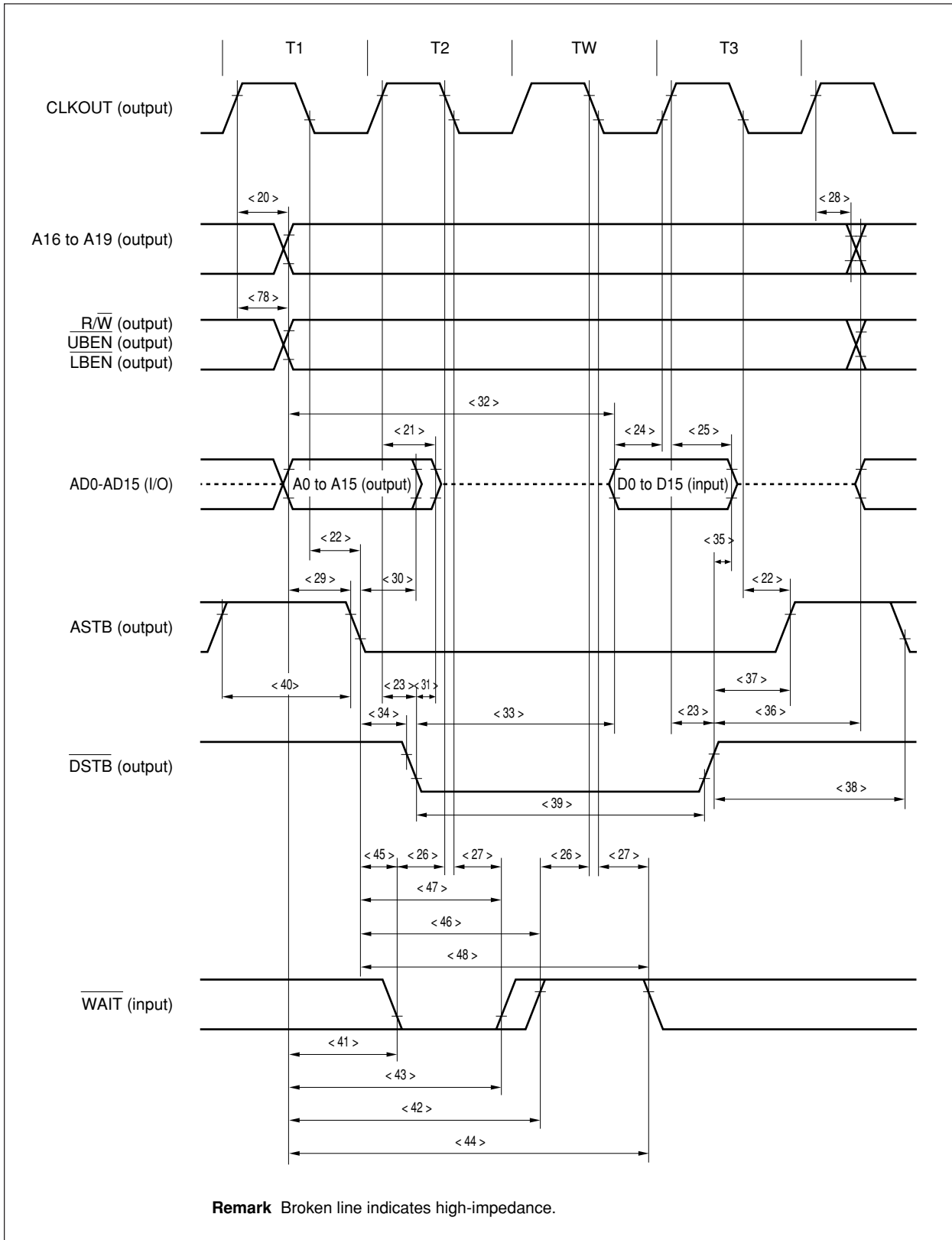| Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<20>	t_{DKA}		3	20	ns
Delay time from CLKOUT↑ to R/$\overline{W}$, $\overline{UBEN}$, $\overline{LBEN}$	<78>	t_{DKA2}		−2	+13	ns
Delay time from CLKOUT↑ to address float	<21>	t_{FKA}		3	15	ns
Delay time from CLKOUT↓ to ASTB	<22>	t_{DKST}		3	15	ns
Delay time from CLKOUT↓ to $\overline{DSTB}$	<23>	t_{DKD}		3	15	ns
Data input setup time (to CLKOUT↑)	<24>	t_{SIDK}		5		ns
Data input hold time (from CLKOUT↑)	<25>	t_{HKID}		5		ns
$\overline{WAIT}$ setup time (to CLKOUT↓)	<26>	t_{SWTK}		5		ns
$\overline{WAIT}$ hold time (from CLKOUT↓)	<27>	t_{HKWT}		5		ns
Address hold time (from CLKOUT↑)	<28>	t_{HKA}		0		ns
Address setup time (to ASTB↓)	<29>	t_{SAST}	−40°C ≤ T_A ≤ +70°C	0.5 T − 10		ns
			70°C < T_A ≤ 85°C	0.5 T − 12		ns
Address hold time (from ASTB↓)	<30>	t_{HSTA}		0.5 T − 10		ns
Delay time from $\overline{DSTB}$↓ to address float	<31>	t_{FDA}			0	ns
Data input setup time (to address)	<32>	t_{SAID}	−40°C ≤ T_A ≤ +70°C		(2 + n) T − 22	ns
			70°C < T_A ≤ 85°C		(2 + n) T − 25	ns
Data input setup time (to $\overline{DSTB}$↓)	<33>	t_{SDID}	−40°C ≤ T_A ≤ +70°C		(1 + n) T − 20	ns
			70°C < T_A ≤ 85°C		(1 + n) T − 24	ns
Delay time from ASTB↓ to $\overline{DSTB}$↓	<34>	t_{DSTD}		0.5 T − 10		ns
Data input hold time (from $\overline{DSTB}$↑)	<35>	t_{HDID}		0		ns
Delay time from $\overline{DSTB}$↑ to address output	<36>	t_{DDA}		(1 + i) T		ns
Delay time from $\overline{DSTB}$↑ to ASTB↑	<37>	t_{DDSTH}		0.5 T − 10		ns
Delay time from $\overline{DSTB}$↑ to ASTB↓	<38>	t_{DDSTL}		(1.5 + i) T − 10		ns
$\overline{DSTB}$ low-level width	<39>	t_{WDL}	−40°C ≤ T_A ≤ +70°C	(1 + n) T − 10		ns
			70°C < T_A ≤ 85°C	(1 + n) T − 13		ns
ASTB high-level width	<40>	t_{WSTH}		T − 10		ns
$\overline{WAIT}$ setup time (to address)	<41>	t_{SAWT1}	n ≥ 1, −40°C ≤ T_A ≤ +70°C		1.5 T − 20	ns
			n ≥ 1, 70°C < T_A ≤ 85°C		1.5 T − 24	ns
	<42>	t_{SAWT2}	n ≥ 1, −40°C ≤ T_A ≤ +70°C		(1.5 + n) T − 20	ns
			n ≥ 1, 70°C < T_A ≤ 85°C		(1.5 + n) T − 24	ns
$\overline{WAIT}$ hold time (from address)	<43>	t_{HAWT1}	n ≥ 1	(0.5 + n) T		ns
	<44>	t_{HAWT2}	n ≥ 1	(1.5 + n) T		ns
$\overline{WAIT}$ setup time (to ASTB↓)	<45>	t_{SSTWT1}	n ≥ 1, −40°C ≤ T_A ≤ +70°C		T − 18	ns
			n ≥ 1, 70°C < T_A ≤ 85°C		T − 20	ns
	<46>	t_{SSTWT2}	n ≥ 1		(1 + n) T − 15	ns
$\overline{WAIT}$ hold time (from ASTB↓)	<47>	t_{HSTWT1}	n ≥ 1	nT		ns
	<48>	t_{HSTWT2}	n ≥ 1	(1 + n) T		ns

Remarks 1. T = t_{CYK}

       2. n indicates the number of wait clocks inserted in the bus cycle. The sampling timing differs when the programmable wait state is inserted.

       3. i indicates the number of idle states (0 or 1) t be inserted in the read cycle.

       4. Be sure to observe at least one of data input hold times t_{HKID} (<25>) and t_{HDID} (<35>).

(5) Read Timing (2/2): 1 wait

Remark Broken line indicates high-impedance.

(6) Write timing (1/2)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<20>	t_{DKA}		3	20	ns
Delay time from CLKOUT↑ to R/$\overline{W}$, $\overline{UBEN}$, $\overline{LBEN}$	<78>	t_{DKA2}		−2	+13	ns
Delay time from CLKOUT↓ to ASTB	<22>	t_{DKST}		3	15	ns
Delay time from CLKOUT↑ to $\overline{DSTB}$	<23>	t_{DKD}		3	15	ns
$\overline{WAIT}$ setup time (to CLKOUT↓)	<26>	t_{SWTK}		5		ns
$\overline{WAIT}$ hold time (from CLKOUT↓)	<27>	t_{HKWT}		5		ns
Address hold time (from CLKOUT↑)	<28>	t_{HKA}		0		ns
Address setup time (to ASTB↓)	<29>	t_{SAST}	−40°C ≤ T_A ≤ +70°C	0.5 T − 10		ns
			70°C < T_A ≤ 85°C	0.5 T − 12		ns
Address hold time (from ASTB↓)	<30>	t_{HSTA}		0.5 T − 10		ns
Delay time from ASTB↓ to $\overline{DSTB}$↓	<34>	t_{DSTD}		0.5 T − 10		ns
Delay time from DSTB↑ to $\overline{ASTB}$↑	<37>	t_{DDSTH}		0.5 T − 10		ns
$\overline{DSTB}$ low-level width	<39>	t_{WDL}	−40°C ≤ T_A ≤ +70°C	(1 + n) T − 10		ns
			70°C < T_A ≤ 85°C	(1 + n) T − 13		ns
$\overline{ASTB}$ high-level width	<40>	t_{WSTH}		T − 10		ns
$\overline{WAIT}$ setup time (to address)	<41>	t_{SAWT1}	n ≥ 1, −40°C ≤ T_A ≤ +70°C		1.5 T − 20	ns
			n ≥ 1, 70°C < T_A ≤ 85°C		1.5 T − 24	ns
	<42>	t_{SAWT2}	n ≥ 1, −40°C ≤ T_A ≤ +70°C		(1.5 + n) T − 20	ns
			n ≥ 1, 70°C < T_A ≤ 85°C		(1.5 + n) T − 24	ns
$\overline{WAIT}$ hold time (from address)	<43>	t_{HAWT1}	n ≥ 1	(0.5 + n) T		ns
	<44>	t_{HAWT2}	n ≥ 1	(1.5 + n) T		ns
$\overline{WAIT}$ setup time (to ASTB↓)	<45>	t_{SSTWT1}	n ≥ 1, −40°C ≤ T_A ≤ +70°C		T − 18	ns
			n ≥ 1, 70°C < T_A ≤ 85°C		T − 20	ns
	<46>	t_{SSTWT2}	n ≥ 1		(1 + n) T − 15	ns
$\overline{WAIT}$ hold time (from ASTB↓)	<47>	t_{HSTWT1}	n ≥ 1	nT		ns
	<48>	t_{HSTWT2}	n ≥ 1	(1 + n) T		ns
Address hold time (from CLKOUT↑)	<49>	t_{DKOD}	−40°C ≤ T_A ≤ +70°C		20	ns
			70°C < T_A ≤ 85°C		23	ns
Delay time from $\overline{DSTB}$↓ to data output	<50>	t_{DDOD}			10	ns
Data output hold time (from CLKOUT↑)	<51>	t_{HKOD}		0		ns
Data output setup time (to $\overline{DSTB}$↑)	<52>	t_{SODD}		(1 + n) T − 15		ns
Data output hold time (from $\overline{DSTB}$↑)	<53>	t_{HDOD}		T − 10		ns

Remarks 1. T = t_{CYK}

2. n indicates the number of wait clocks inserted in the bus cycle. The sampling timing differs when the programmable wait state is inserted.
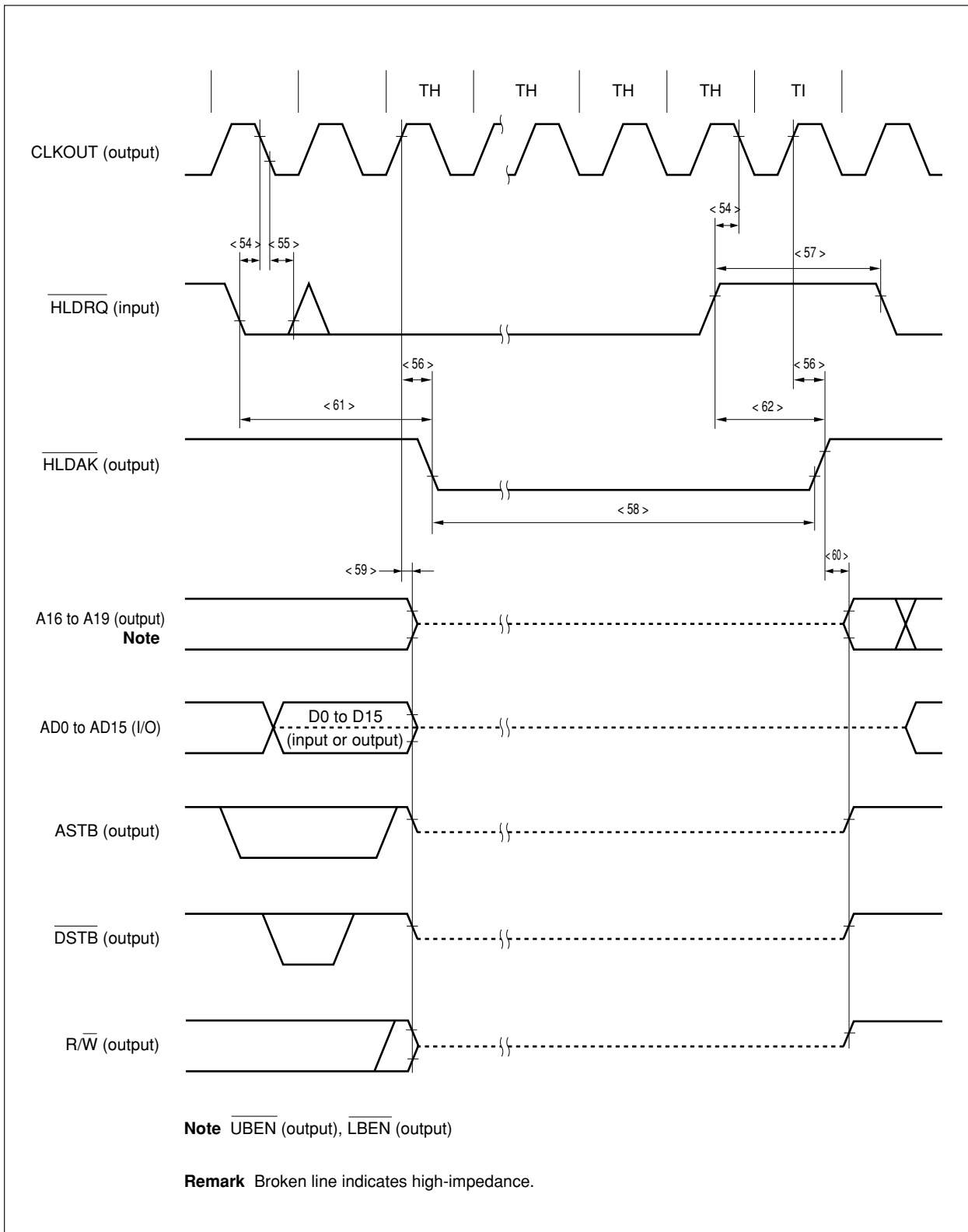
(6) Write timing (2/2): 1 wait

Remark Broken line indicates high-impedance.
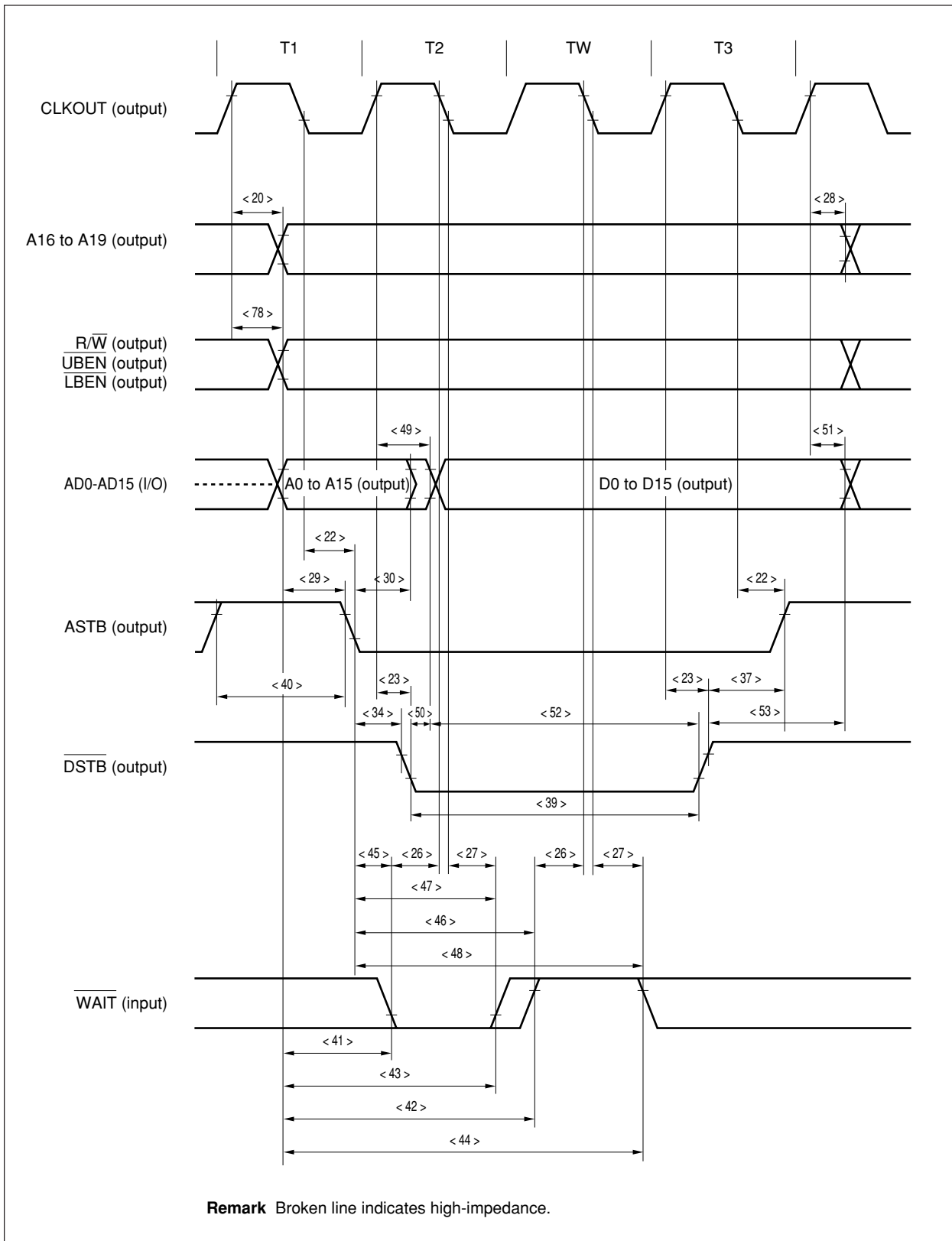
(7) Bus hold timing (1/2)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
$\overline{\text{HLDRQ}}$ setup time (to CLKOUT↓)	<54>	t_{SHOK}		5		ns
$\overline{\text{HLDRQ}}$ hold time (from CLKOUT↓)	<55>	t_{HKHQ}		5		ns
Delay time from $\overline{\text{HLDAK}}$ to CLKOUT↑	<56>	t_{DKHA}			20	ns
$\overline{\text{HLDRQ}}$ high-level width	<57>	t_{WHQH}		T + 10		ns
$\overline{\text{HLDAK}}$ low-level width	<58>	t_{WHAL}	$-40°C \leq T_A \leq +70°C$	T − 10		ns
			$70°C < T_A \leq 85°C$	T − 12		ns
Delay time from CLKOUT↑ to bus float	<59>	t_{DKF}			20	ns
Delay time from $\overline{\text{HLDAK}}$↑ to bus output	<60>	t_{DHAC}		−3		ns
Delay time from $\overline{\text{HLDRQ}}$↓ to $\overline{\text{HLDAK}}$↓	<61>	t_{DHQHA1}			(2 n + 7.5) T + 20	ns
Delay time from $\overline{\text{HLDRQ}}$↑ to $\overline{\text{HLDAK}}$↑	<62>	t_{DHQHA2}		0.5 T	1.5 T + 20	ns

Remarks 1. T = t_{CYK}

2. n indicates the number of wait clocks inserted in the bus cycle. The sampling timing differs when the programmable wait state is inserted.

(7) Bus hold timing (2/2)

Note $\overline{\text{UBEN}}$ (output), $\overline{\text{LBEN}}$ (output)

Remark Broken line indicates high-impedance.

(8) Interrupt timing

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
NMI width, high	<63>	t_{WNIH}		500		ns
NMI width, low	<64>	t_{WNIL}		500		ns
INTPn width, high	<65>	t_{WITH}	n = 110 to 113, 120 to 123, 130 to 133, 140 to 143	3 T + 10		ns
INTPn width, low	<66>	t_{WITL}	n = 110 to 113, 120 to 123, 130 to 133, 140 to 143	3 T + 10		ns

Remark T = t_{CYK}

Remark n = 110 to 113, 120 to 123, 130 to 133, 140 to 143
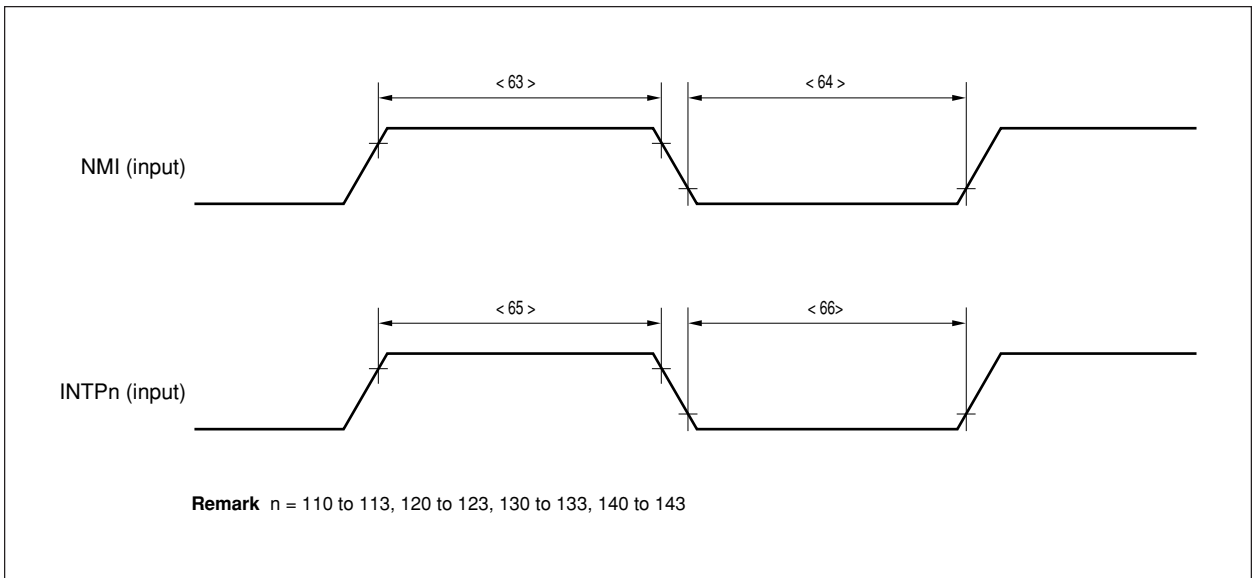
(9) CSI timing (1/2)

(a) Master mode

(i) CSI0 to CSI2 timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{SCKn}$ cycle	<67>	t_{CYSK1}	Output	120		ns
$\overline{SCKn}$ high-level width	<68>	t_{WSKH1}	Output	$0.5\ t_{CYSK1} - 20$		ns
$\overline{SCKn}$ low-level width	<69>	t_{WSKL1}	Output	$0.5\ t_{CYSK1} - 20$		ns
SIn setup time (to $\overline{SCKn}\uparrow$)	<70>	t_{SSISK1}		30		ns
SIn hold time (from $\overline{SCKn}\uparrow$)	<71>	t_{HSKSI1}		0		ns
SOn output delay time (from $\overline{SCKn}\downarrow$)	<72>	t_{DSKSO1}			18	ns
SOn output hold time (from $\overline{SCKn}\uparrow$)	<73>	t_{HSKSO1}		$0.5\ t_{CYSK1} - 5$		ns

Remark n = 0 to 2

(ii) CSI3 timing

Parameter	Symbol		Conditions		MIN.	MAX.	Unit
$\overline{SCK3}$ cycle	<67>	t_{CYSK3}	Output	$R_L = 1.5$ kΩ $C_L = 50$ pF	500		ns
$\overline{SCK3}$ high-level width	<68>	t_{WSKH3}	Output		$0.5\ t_{CYSK3} - 70$		ns
$\overline{SCK3}$ low-level width	<69>	t_{WSKL3}	Output		$0.5\ t_{CYSK3} - 70$		ns
SI3 setup time (to $\overline{SCK3}\uparrow$)	<70>	t_{SSISK3}			100		ns
SI3 hold time (from $\overline{SCK3}\uparrow$)	<71>	t_{HSKSI3}			50		ns
SO3 output delay time (from $\overline{SCK3}\downarrow$)	<72>	t_{DSKSO3}	$R_L = 1.5$ KΩ $C_L = 50$ pF			150	ns
SO3 output hold time (from $\overline{SCK3}\uparrow$)	<73>	t_{HSKSO3}			$0.5\ t_{CYSK3} - 5$		ns

Remark R_L and C_L are the load resistance and load capacitance respectively of the $\overline{SCK3}$ and SO3 output lines.

(b) Slave mode

(i) CSI0 to CSI2 timing

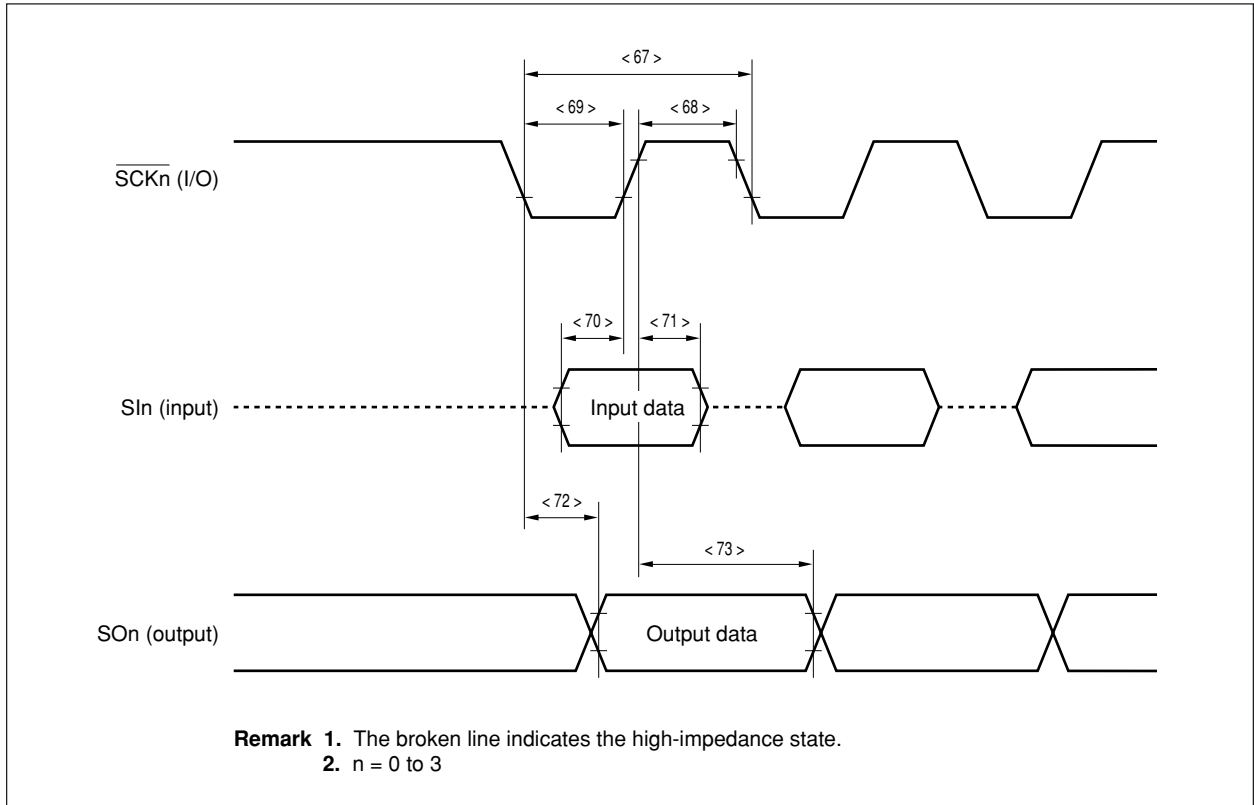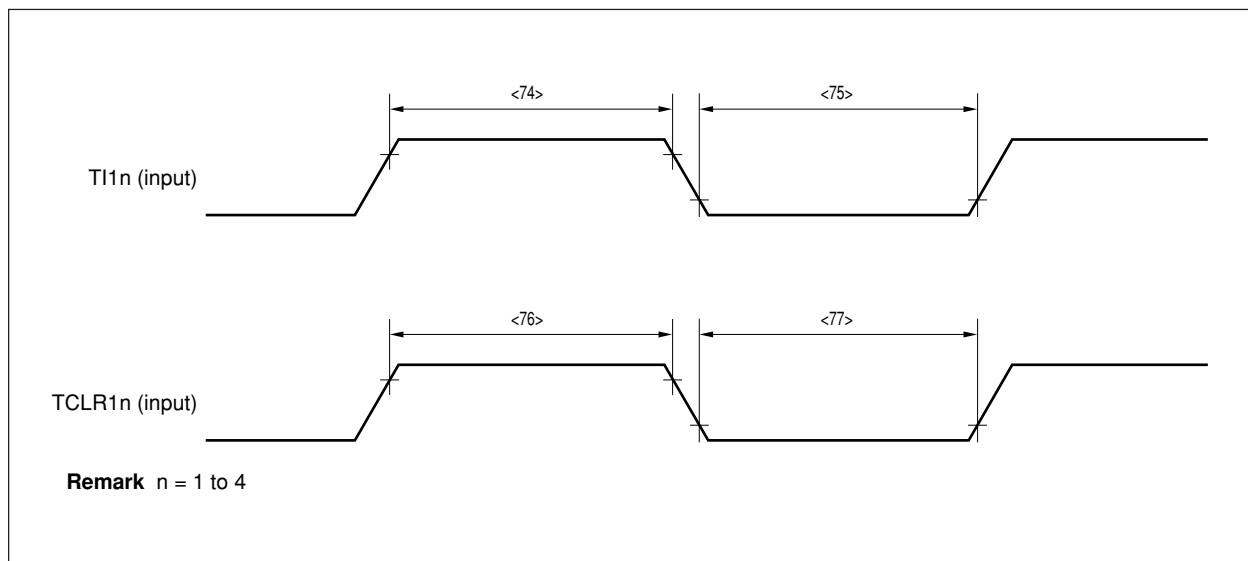| Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{SCKn}$ cycle	<67>	t_{CYSK2}	Input	120		ns
$\overline{SCKn}$ high-level width	<68>	t_{WSKH2}	Input	30		ns
$\overline{SCKn}$ low-level width	<69>	t_{WSKL2}	Input	30		ns
SIn setup time (to $\overline{SCKn}\uparrow$)	<70>	t_{SSISK2}		10		ns
SIn hold time (from $\overline{SCKn}\uparrow$)	<71>	t_{HSKSI2}		10		ns
SOn output delay time (from $\overline{SCKn}\downarrow$)	<72>	t_{DSKSO2}			30	ns
SOn output hold time (from $\overline{SCKn}\uparrow$)	<73>	t_{HSKSO2}		t_{WSKH2}		ns

Remark n = 0 to 2

(9) CSI timing (2/2)

(ii) CSI3 timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{SCK3}$ cycle	<67>	t_{CYSK4}	Input	500		ns
$\overline{SCK3}$ high-level width	<68>	t_{WSKH4}	Input	180		ns
$\overline{SCK3}$ low-level width	<69>	t_{WSKL4}	Input	180		ns
SI3 setup time (to $\overline{SCK3}\uparrow$)	<70>	t_{SSISK4}		100		ns
SI3 hold time (from $\overline{SCK3}\uparrow$)	<71>	t_{HSKSI4}		50		ns
SO3 output delay time (from $\overline{SCK3}\downarrow$)	<72>	t_{DSKSO4}	$R_L = 1.5$ kΩ		150	ns
SO3 output hold time (from $\overline{SCK3}\uparrow$)	<73>	t_{HSKSO4}	$C_L = 50$ pF	t_{WSKH4}		ns

Remark R_L and C_L are the load resistance and load capacitance respectively of the $\overline{SCK3}$ and SO3 output lines.

Remark 1. The broken line indicates the high-impedance state.
      2. n = 0 to 3

(10) RPU timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
TI1n high-level width	<74>	t$_{WTIH}$		3 T + 10		ns
TI1n low-level width	<75>	t$_{WTIL}$		3 T + 10		ns
TCLR1n high-level width	<76>	t$_{WTCH}$		3 T + 10		ns
TCLR1n low-level width	<77>	t$_{WTCL}$		3 T + 10		ns

Remark T = t$_{CYK}$

TI1n (input)

TCLR1n (input)

Remark n = 1 to 4

A/D Converter Characteristics (T$_A$ = −40 to +85°C, V$_{DD}$ = AV$_{DD}$ = 5 V ±10%, V$_{SS}$ = AV$_{SS}$ = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	—		10	10	10	bit
Overall error[Note 1]	—	4.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$			±0.4	%FSR
	—	3.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$			±0.7	%FSR
Quantization error	—				±1/2	LSB
Conversion time	t$_{CONV}$	4.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$	60			t$_{CYK}$
		3.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$	60			t$_{CYK}$
Sampling time	t$_{SAMP}$	4.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$	10			t$_{CYK}$
		3.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$	10			t$_{CYK}$
Zero-scale error[Note 1]	—	4.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$		±1.5	±3.5	LSB
	—	3.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$		±1.5	±4.5	LSB
Full-scale error[Note 1]	—	4.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$		±1.5	±2.5	LSB
	—	3.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$		±1.5	±4.5	LSB
Non-linearity error[Note 1]	—	4.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$		±1.5	±2.5	LSB
	—	3.5 V ≤ AV$_{REF1}$ ≤ AV$_{DD}$		±1.5	±4.5	LSB
Analog input voltage[Note 2]	V$_{IAN}$		−0.3		AV$_{DD}$ + 0.3	V
Reference voltage	AV$_{REF1}$		3.5		AV$_{DD}$	V
AV$_{REF1}$ current	AI$_{REF1}$			1.2	3.0	mA
AV$_{DD}$ supply current	AI$_{DD}$			2.3	6.0	mA

Notes 1. Except quantization error.

     2. The conversion result is 000H when V$_{IAN}$ = 0.

       Converted with 10-bit resolution when 0 < V$_{IAN}$ < AV$_{REF1}$.

       The conversion result is 3FFH when AV$_{REF1}$ ≤ V$_{IAN}$ ≤ AV$_{DD}$.

D/A Converter Characteristics (T$_A$ = –40 to +85°C, V$_{DD}$ = AV$_{DD}$ = 5 V ±10%, V$_{SS}$ = AV$_{SS}$ = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	—		8	8	8	bit
Overall error	—	Load conditions: 2 MΩ, 30 pF AV$_{REF2}$ = V$_{DD}$ AV$_{REF3}$ = 0			0.8	%
	—	Load conditions: 2 MΩ, 30 pF AV$_{REF2}$ = 0.75 V$_{DD}$ AV$_{REF3}$ = 0.25 V$_{DD}$			1.0	%
	—	Load conditions: 4 MΩ, 30 pF AV$_{REF2}$ = V$_{DD}$ AV$_{REF3}$ = 0			0.6	%
	—	Load conditions: 4 MΩ, 30 pF AV$_{REF2}$ = 0.75 V$_{DD}$ AV$_{REF3}$ = 0.25 V$_{DD}$			0.8	%
Settling time	—	Load conditions: 2 MΩ, 30 pF			10	μs
Output resistance	RO			8		kΩ
AV$_{REF2}$ input voltage	AV$_{REF2}$		0.75V$_{DD}$		V$_{DD}$	V
AV$_{REF3}$ input voltage	AV$_{REF3}$		0		0.25V$_{DD}$	V
Resistance between AV$_{REF2}$ and AV$_{REF3}$	R$_{AIREF}$	DACS0, DACS1 = 55H	2	4		kΩ

3.2 Flash Memory Programming Mode

Basic Characteristics (T_A = 10 to 40°C (when rewriting), T_A = –40 to +85°C (when not rewriting), V_DD = AV_DD = 5 V ±10%, V_SS = AV_SS = 0 V))

(1) μPD70F3003A (all ranks), 70F3025A (except K, E, P, X rank)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating frequency	ϕ		10		33	MHz
V_PP supply voltage	V_PP1	During flash memory programming	9.7	10.3	10.6	V
	V_PPL	V_PP low-level detection	–0.5		0.2V_DD	V
	V_PPM	V_PP, V_DD level detection	0.8V_DD		1.2V_DD	V
	V_PPH	V_PP high-voltage level detection	9.7	10.3	10.6	V
V_DD supply current	I_DO	V_PP = V_PP1			$3.0 \times \phi + 25$	mA
V_PP supply current	I_PP	V_PP = 10.3 V			200	mA
Step erase time	t_ER	**Note 1**		0.2		s
Overall erase time per area	t_ERA	When the step erase time = 0.2 s, **Note 2**			40	s/area
Write-back time	t_WB	**Note 3**		5		ms
Number of write-backs per write-back command	C_WB	When the write-back time = 5 ms, **Note 4**			50	Count/write-back command
Number of erase/write-backs	C_ERWB				16	Count
Step writing time	t_WT	**Note 5**		50		μs
Overall writing time per word	t_WTW	When the step writing time = 50 μs (1 word = 4 bytes), **Note 6**	50		500	μs/word
Number of rewrites per area	C_ERWR	1 erase + 1 write after erase = 1 rewrite, **Note 7**		20		Count/area

Notes 1. The recommended setting value of the step erase time is 0.2 s.

2. The prewrite time prior to erasure and the erase verify time (write-back time) are not included.

3. The recommended setting value of the step erase time is 5 ms.

4. Write-back is executed once by the issuance of the write-back command. Therefore, the retry count must be the maximum value minus the number of commands issued.

5. The recommended setting value of the step writing time is 50 μs.

6. 100 μs is added to the actual writing time per word. The internal verify time during and after the writing is not included.

7. When writing initially to shipped products, it is counted as one rewrite for both "erase to write" and "write only".

Example (P: Write, E: Erase)

Shipped product ⟶ P→ E → P → E → P: 3 rewrites

Shipped product → E → P → E → P → E → P: 3 rewrites

Cautions 1. V_{PP} **pull-down resistance value (RVPP) is recommended to be in the range 5 kΩ to 15 kΩ.**

        2. Set the transfer rate between programmer and device as follows.

           CSI0:   0.2 to 1 MHz

           UART0: 4,800 to 76,800 bps

Remarks 1. When the PG-FP3 is used, a time parameter required for writing/erasing by downloading parameter files is automatically set. Do not change the settings unless otherwise specified.

        2. Area 0 = 00000H to 1FFFFH, area 1 = 20000H to 3FFFFH (area 1 is provided in the μPD70F3025A only)

        3. The rank is indicated by the 5th character from the left in the lot number.

        4. The I rank applies to engineering samples (ES) only. The operation of an ES is not guaranteed.

        5. ϕ: Internal system clock frequency

(2) μPD70F3025A (X rank)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating frequency	ϕ	**Note 1**	10		33	MHz
VPP supply voltage	VPP1	During flash memory programming	9.7	10.3	10.6	V
	VPPL	VPP low-level detection	−0.5		0.2VDD	V
	VPPM	VPP, VDD level detection	0.8VDD		1.2VDD	V
	VPPH	VPP high-voltage level detection	9.7	10.3	10.6	V
VDD supply current	IDD	VPP= VPP1			$3.0 \times \phi + 25$	mA
VPP supply current	IPP	VPP= 10.3 V			200	mA
Step erase time	tER	**Note 1**		2		s
Overall erase time per area	tERA	When the step erase time = 2 s, **Note 2**			40	s/area
Step writing time	tWT	**Note 3**		200		μs
Overall writing time per word	tWTW	When the step writing time = 200 μs (1 word = 4 bytes), **Note 4**	200		2000	μs/word
Number of rewrites per area	CERWR	1 erase + 1 write after erase = 1 rewrite, **Note 5**		20		Count/area

Notes 1. The recommended setting value of the step erase time is 2 s.

   2. The prewrite time prior to erasure and the erase verify time (write-back time) are not included.

   3. The recommended setting value of the step writing time is 200 μs.

   4. 100 μs is added to the actual writing time per word. The internal verify time during and after the writing is not included.

   5. When writing initially to shipped products, it is counted as one rewrite for both "erase to write" and "write only".

Example (P: Write, E: Erase)

   Shipped product ⟶ P → E → P → E → P: 3 rewrites

   Shipped product → E → P → E → P → E → P: 3 rewrites

Cautions 1. **VPP pull-down resistance value (RVPP) is recommended to be in the range 5 kΩ to 15 kΩ.**

   2. **Set the transfer rate between programmer and device as follows.**

   CSI0:   0.2 to 1 MHz

   UART0: 4,800 to 76,800 bps

Remarks 1. When the PG-FP3 is used, a time parameter required for writing/erasing by downloading parameter files is automatically set. Do not change the settings unless otherwise specified.

   2. Area 0 = 00000H to 1FFFFH, area 1 = 20000H to 3FFFFH

   3. The rank is indicated by the 5th character from the left in the lot number.

   4. The K, E, P, and X rank products do not support handshake mode. The I rank applies to engineering samples (ES) only. The operation of an ES is not guaranteed.

   5. ϕ: Internal system clock frequency

★ **4. PACKAGE DRAWING**

100-PIN PLASTIC LQFP (FINE PITCH) (14x14)

detail of lead end
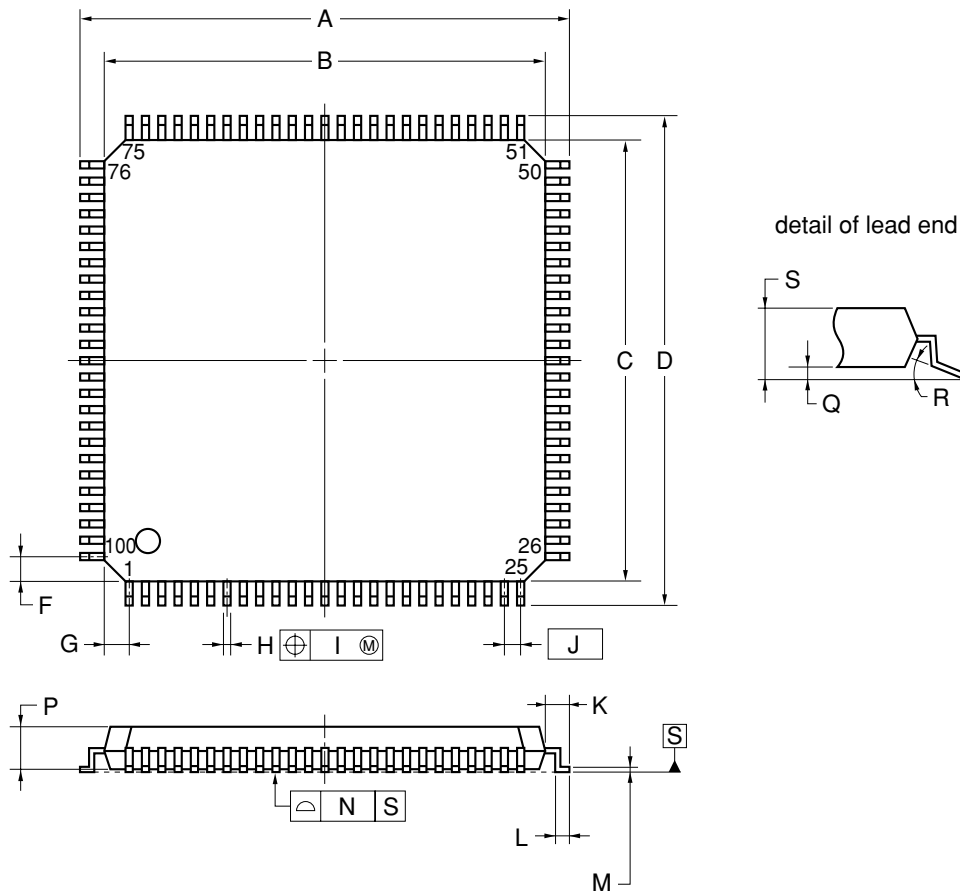
NOTE

Each lead centerline is located within 0.08 mm of
its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	16.00±0.20
B	14.00±0.20
C	14.00±0.20
D	16.00±0.20
F	1.00
G	1.00
H	$0.22^{+0.05}_{-0.04}$
I	0.08
J	0.50 (T.P.)
K	1.00±0.20
L	0.50±0.20
M	$0.17^{+0.03}_{-0.07}$
N	0.08
P	1.40±0.05
Q	0.10±0.05
R	$3°^{+7°}_{-3°}$
S	1.60 MAX.

S100GC-50-8EU, 8EA-2

5. RECOMMENDED SOLDERING CONDITIONS

The μPD70F3003A, 70F3025A, and 70F3003A(A) should be soldered and mounted under the following recommended conditions.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Table 5-1. Surface Mounting Type Soldering Conditions

(1) μ**PD70F3003AGC-33-8EU:**   100-pin plastic LQFP (fine pitch) (14 $\times$ 14)
     μ**PD70F3025AGC-33-8EU:**   100-pin plastic LQFP (fine pitch) (14 $\times$ 14)

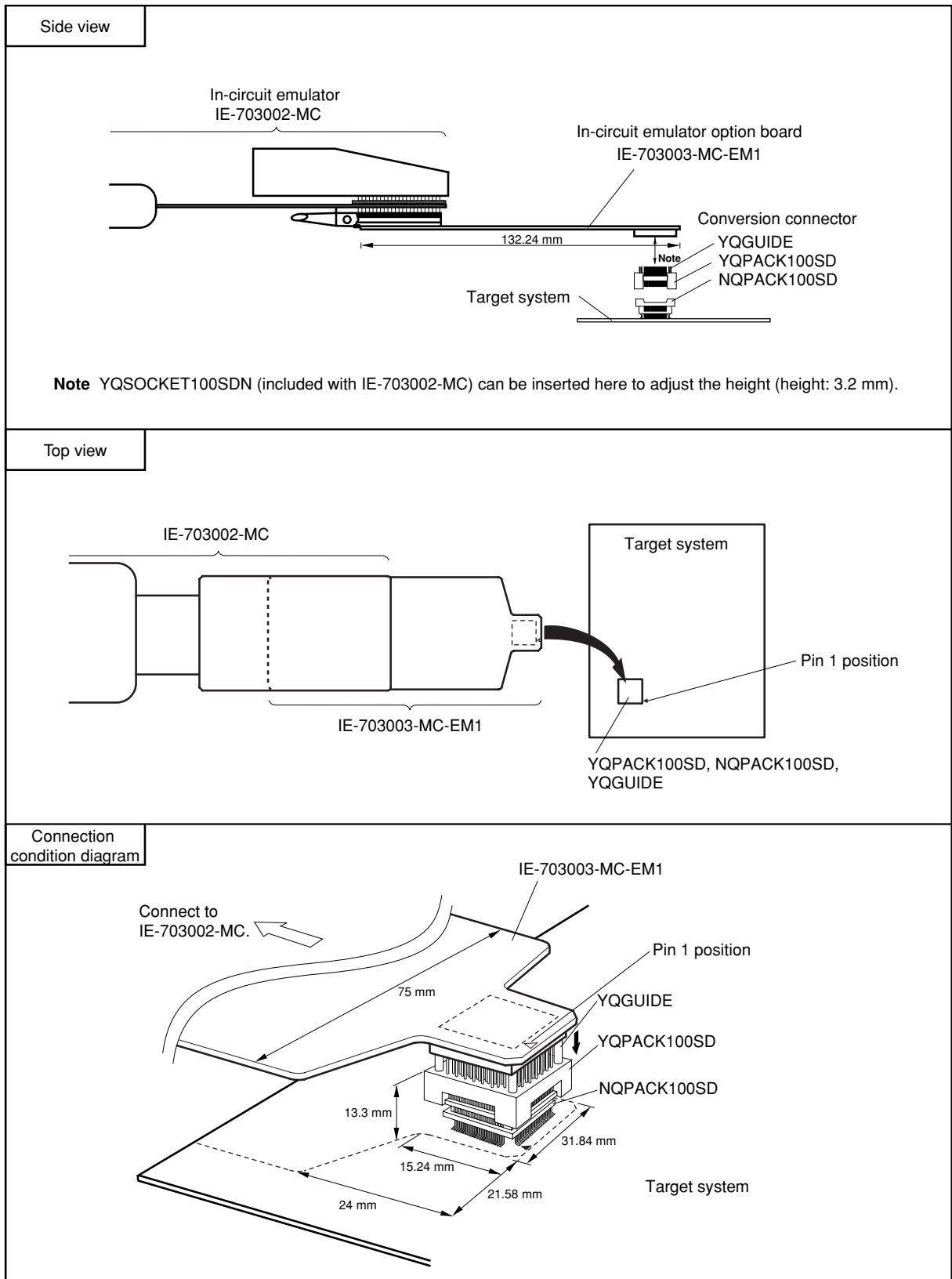| Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Three times or less, Exposure limit: 3 days**Note** (after that, prebake at 125°C for 10 to 72 hours)	IR35-103-3
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Three times or less, Exposure limit: 3 days**Note** (after that, prebake at 125°C for 10 to 72 hours)	VP15-103-3
Partial heating	Pin temperature: 300°C max., Time 3 seconds max. (per pin row)	—

Note   After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Remark   For soldering methods and conditions other than those recommended above, consult an NEC Electronics sales representative.

★ **(2)** μ**PD70F3003AGC-33-8EU-A: 100-pin plastic LQFP (fine pitch) (14 $\times$ 14)**
     μ**PD70F3025AGC-33-8EU-A: 100-pin plastic LQFP (fine pitch) (14 $\times$ 14)**

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 260°C, Time: 60 seconds max. (at 220°C or higher), Count: Three times or less, Exposure limit: 7 days**Note** (after that, prebake at 125°C for 20 to 72 hours)	IR60-207-3
Wave soldering	For details,consult an NEC Electronics sales representative.	—
Partial heating	Pin temperature: 350°C max., Time: 3 seconds max. (per pin row)	—

Note   After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Remarks 1.   Products with -A at the end of the part number are lead-free products.
        2.   For soldering methods and conditions other than those recommended above, consult an NEC Electronics sales representative.

★ **(3)** μ**PD70F3003AGC(A)-33-8EU: 100-pin plastic LQFP (fine pitch) (14** $\times$ **14)**

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less, Exposure limit: 3 days**Note** (after that, prebake at 125°C for 10 to 72 hours)	IR35-103-2
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Two times or less, Exposure limit: 3 days**Note** (after that, prebake at 125°C for 10 to 72 hours)	VP15-103-2
Partial heating	Pin temperature: 300°C max., Time 3 seconds max. (per pin row)	—

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Remark For soldering methods and conditions other than those recommended above, consult an NEC Electronics sales representative.

★ **APPENDIX NOTES ON TARGET SYSTEM DESIGN**

The following shows a diagram of the connection conditions between the in-circuit emulator option board and conversion connector. Design your system making allowances for conditions such as the form of parts mounted on the target system as shown below.

Side view

In-circuit emulator
IE-703002-MC

In-circuit emulator option board
IE-703003-MC-EM1

Conversion connector
YQGUIDE
YQPACK100SD
NQPACK100SD

132.24 mm

Note

Target system

Note YQSOCKET100SDN (included with IE-703002-MC) can be inserted here to adjust the height (height: 3.2 mm).

Top view

IE-703002-MC

Target system

Pin 1 position

IE-703003-MC-EM1

YQPACK100SD, NQPACK100SD,
YQGUIDE

Connection
condition diagram

IE-703003-MC-EM1

Connect to
IE-703002-MC.

Pin 1 position

75 mm

YQGUIDE

YQPACK100SD

NQPACK100SD

13.3 mm

31.84 mm

15.24 mm

Target system

21.58 mm

24 mm

────── **NOTES FOR CMOS DEVICES** ──────

① **VOLTAGE APPLICATION WAVEFORM AT INPUT PIN**

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).

② **HANDLING OF UNUSED INPUT PINS**

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ **PRECAUTION AGAINST ESD**

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

④ **STATUS BEFORE INITIALIZATION**

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

⑤ **POWER ON/OFF SEQUENCE**

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

⑥ **INPUT OF SIGNAL DURING POWER OFF STATE**

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

Related document: *μ*PD703003A, 703004A, 703025A, 703003A(A), 703025A(A) Data Sheet (U13188E)

Reference Materials   Electrical Characteristics for Microcomputer (U15170J**Note**)

Note   This document number is that of Japanese version.

The related documents indicated in this publication may include preliminary versions. However, preliminary versions are not marked as such.

Regional Information

Some information contained in this document may vary from country to country. Before using any NEC Electronics product in your application, please contact the NEC Electronics office in your country to obtain a list of authorized representatives and distributors. They will verify:

- Device availability

- Ordering information

- Product release schedule

- Availability of related technical literature

- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)

- Network requirements

In addition, trademarks, registered trademarks, export restrictions, and other legal issues may also vary from country to country.

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